

Photonic Integrated Circuit for Channelizing RF Signals

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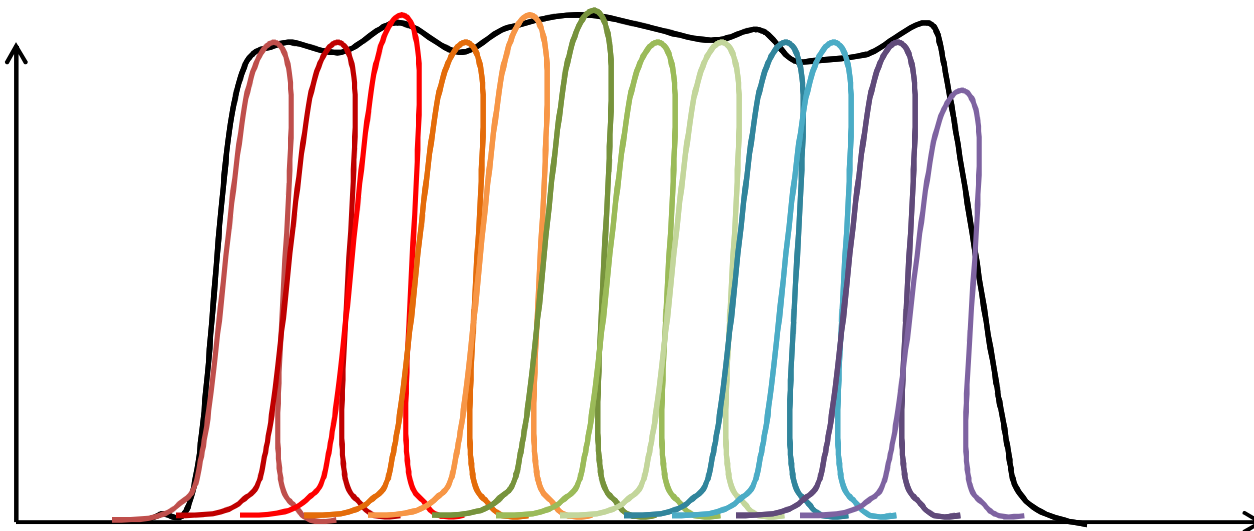
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CLEO, San Jose, CA

June 11, 2013

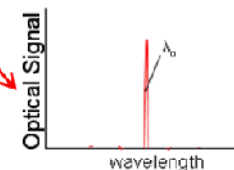
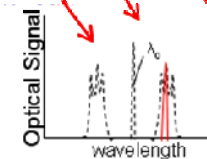
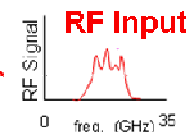
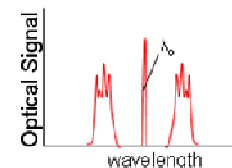
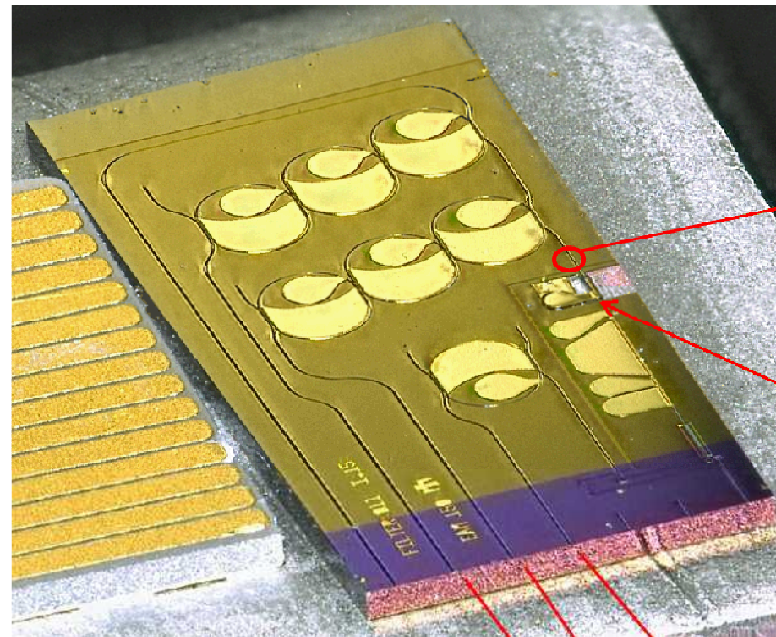
Motivation

- Electronic digital signal processing is limited for wideband RF signals
 - Wideband signals have to be channelized to passbands of a few GHz
 - They are then down-converted to frequencies compatible with A-to-D converters
 - Electronic channelizers are physically large and have fixed frequency characteristics
 - Limiting the application space



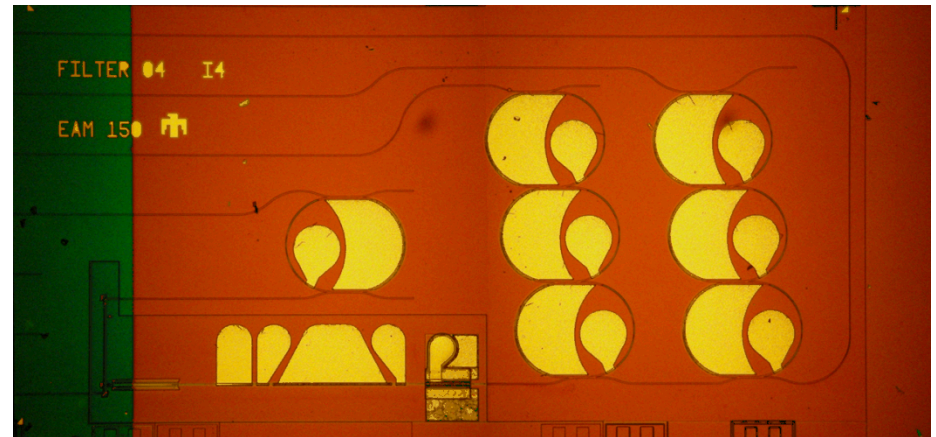
Monolithic RF Channelizing PIC

- Why optical RF channelizing?
 - Low SWaP
 - Wide bandwidth (1-50 GHz)
 - Made possible by InP-based photonic integrated circuits (PICs)
- Channelize RF signals for further analysis
- Monolithic integration enables compact, highly functional photonic integrated circuits (PICs)
- Tunable filters enable accurate placement across the frequency band



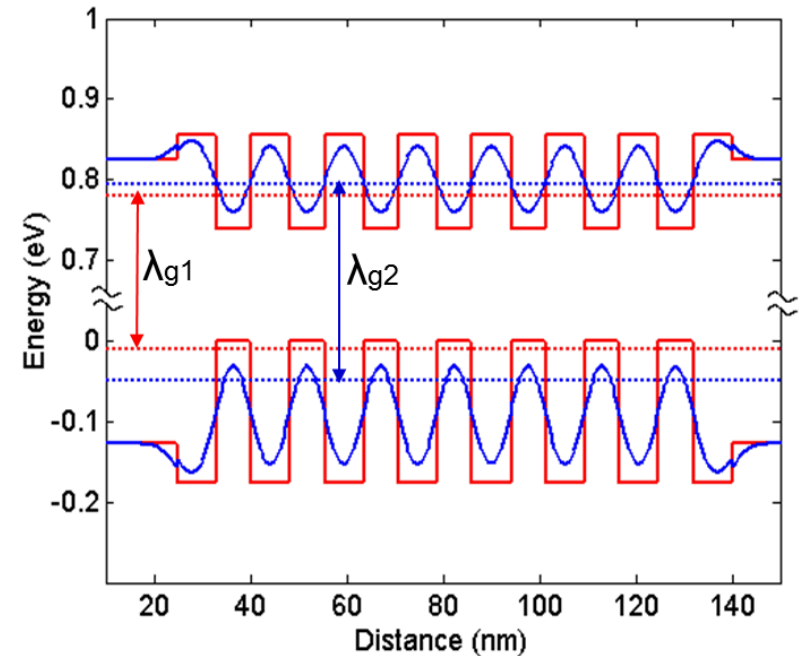
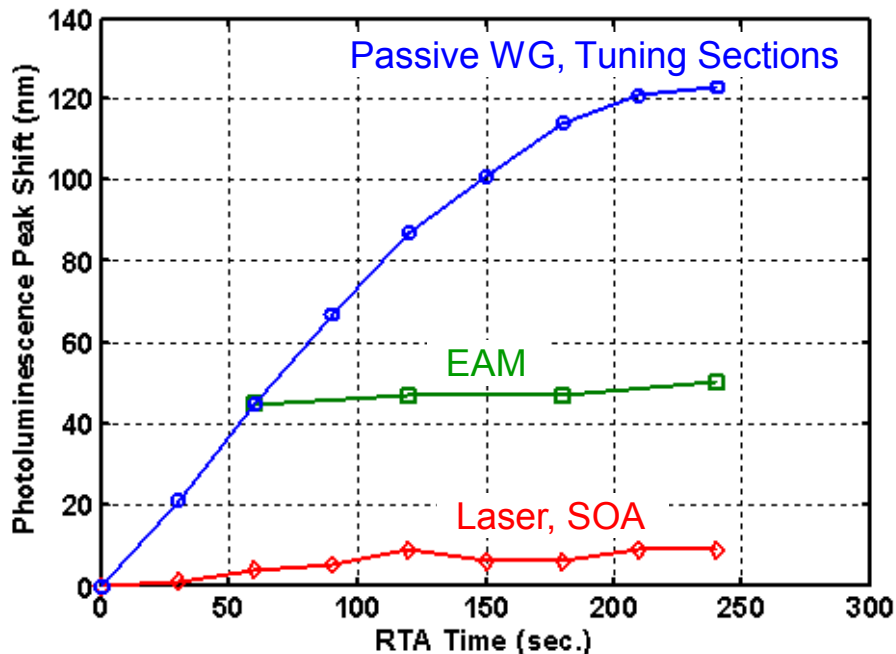
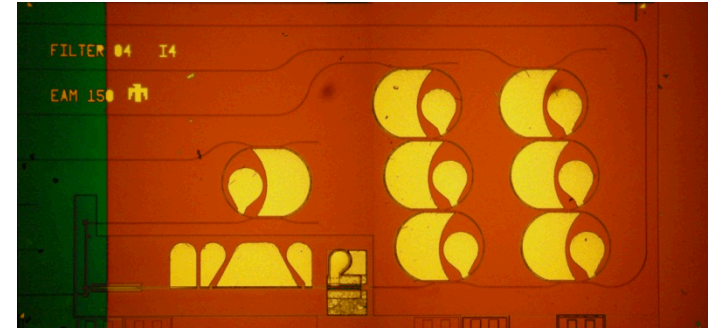
Monolithic RF Channelizing PIC

- Important PIC features
 - Cascaded ring resonator filters
 - Tunable over 10's GHz
 - GHz-class pass bands
 - 65 GHz free spectral range
 - Integrated laser-modulator
 - Reduces coupling losses
 - Signal to EAM provides the RF input
 - Integrated extra filter for wavelength monitoring



Monolithic Integration Platform

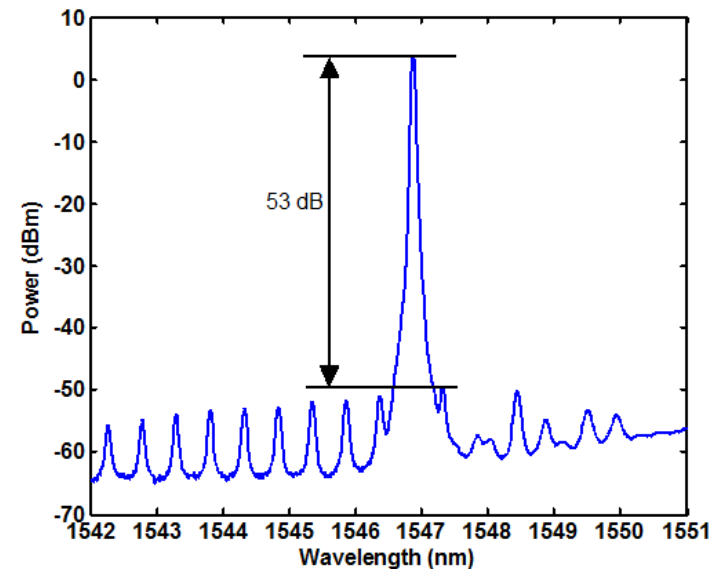
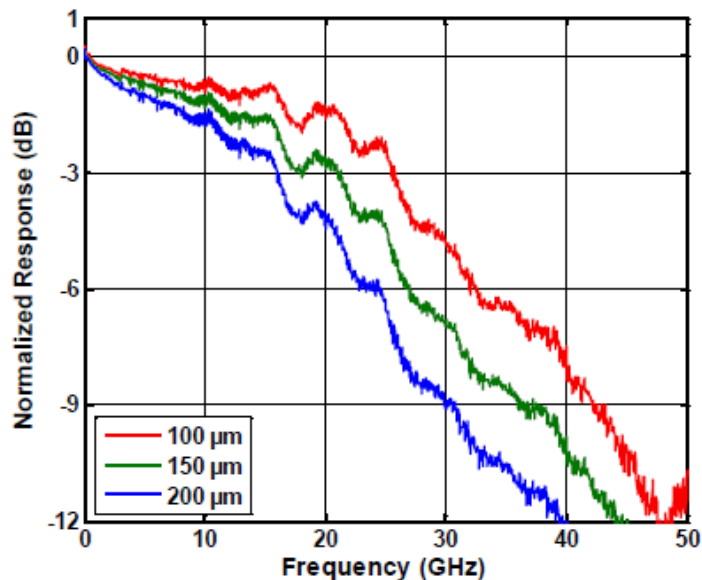
- Quantum well intermixing
 - Metastable interface between well/barrier
 - Add catalyst to enhance interdiffusion
 - Reshaping increases the energy level
 - Reduces the bandgap wavelength
 - Capable >2 bandedges with same epitaxial base



Laser-modulator

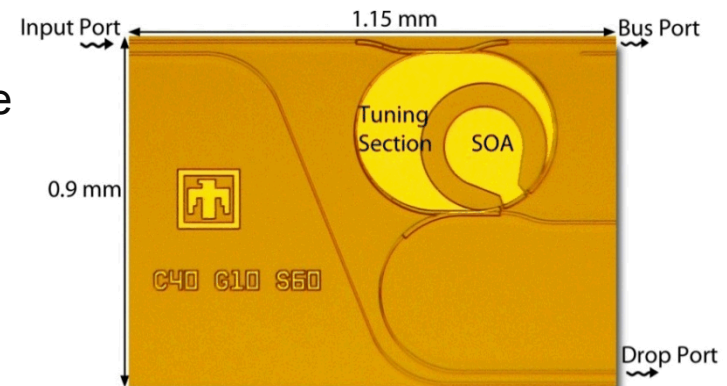
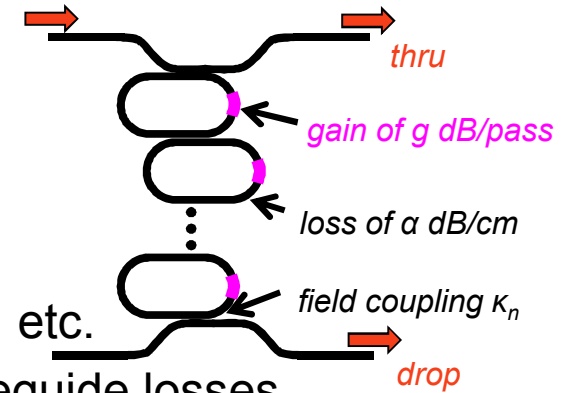
- DBR laser
 - >50 dB SMSR
 - Laser tunable over several nm
 - Continuous tuning over 0.3 nm
- Electroabsorption modulator
 - Bandwidth >20 GHz for 150 μm length
- Ridge waveguide design

DBR Laser –EAM

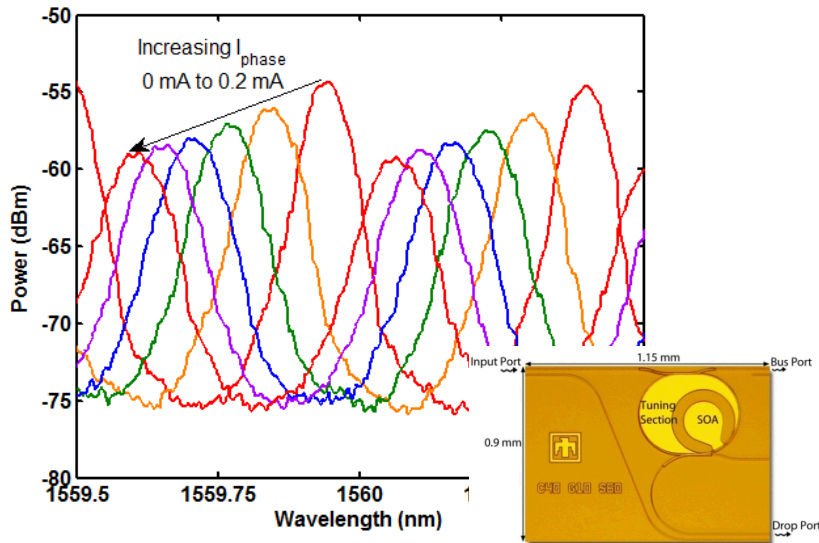


Design of Active Ring Filters

- Active ring resonators offer:
 - Compact size
 - Low, or zero, back reflection
 - Monolithic integration with lasers, modulators, SOA, etc.
 - Gain elements can be used to compensate for waveguide losses
 - Loss, couplers, and optical gain needs to be tightly controlled to achieve designed bandwidth, profile, extinction ratio and low noise
- Our approach
 - Couplers designed for 1-5 GHz linewidth
 - Manipulate loss through filter
 - Length and total gain designed for low noise
 - Tuning section
 - Current injection

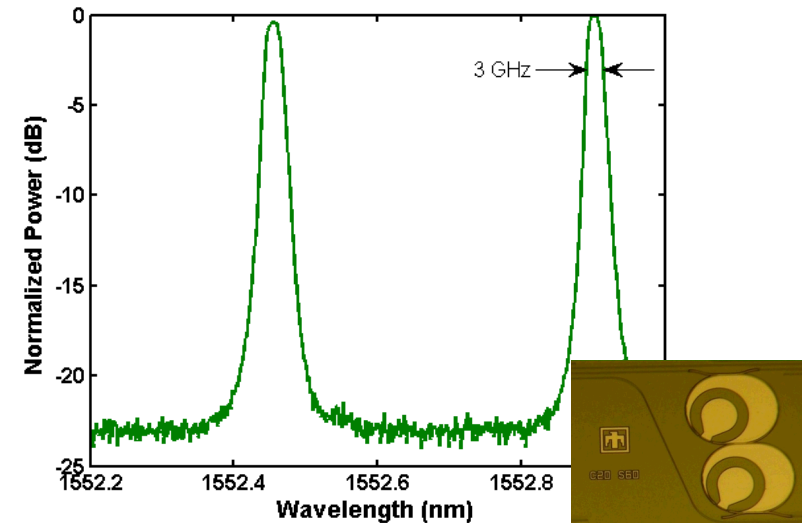


Filters: Previous Work



- Tuning of single ring resonator
 - Tunable over the entire free spectral range
- Developed experimentally verified models for the InP-based resonators

“InP Tunable Ring Resonator Filters”, Photonics West 2012



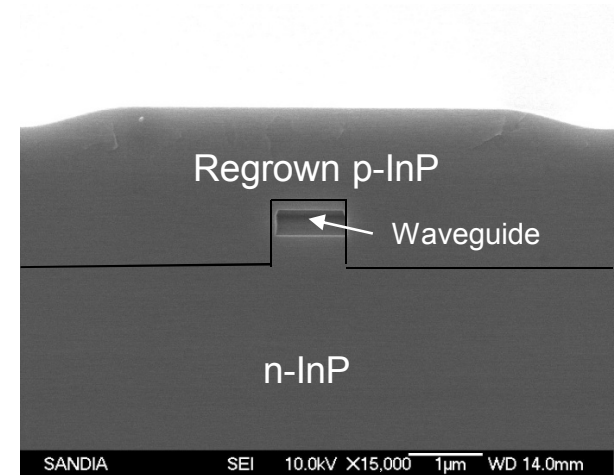
- Cascaded 2-ring resonator
 - 3 GHz 3-dB optical bandwidth
 - >20 dB extinction
 - Quality factor of 65,000

“Cascaded Double Ring Resonator Filter with Integrated SOAs” OFC 2011

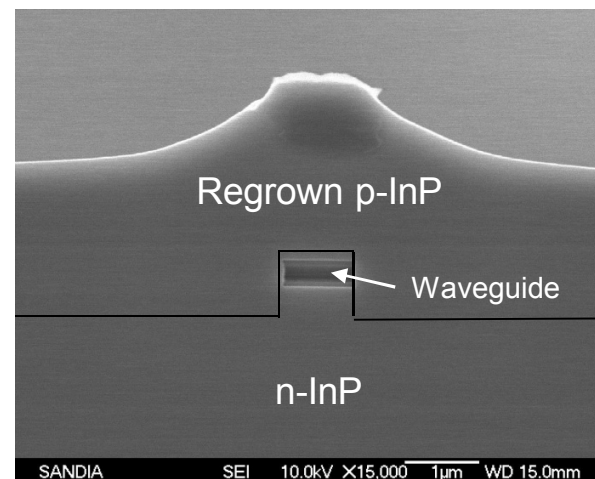
Filters: Waveguides

- Low loss waveguides are necessary for high Q filters
- Couplers need to be tightly controlled to achieve designed bandwidths
- Buried heterostucture advantages
 - Waveguide thickness defined by epitaxial material
 - Semiconductor etch only defines guiding width and coupler gap
 - Devices are essentially not affected by variations in etch depth

Waveguides in [011]

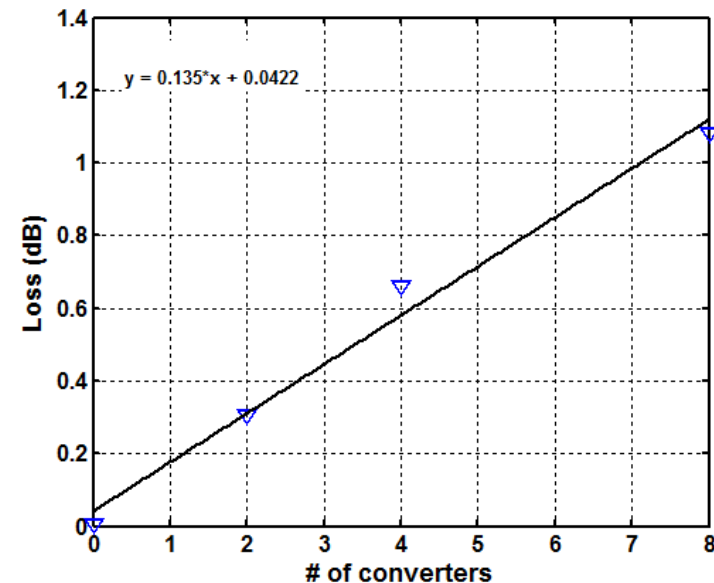
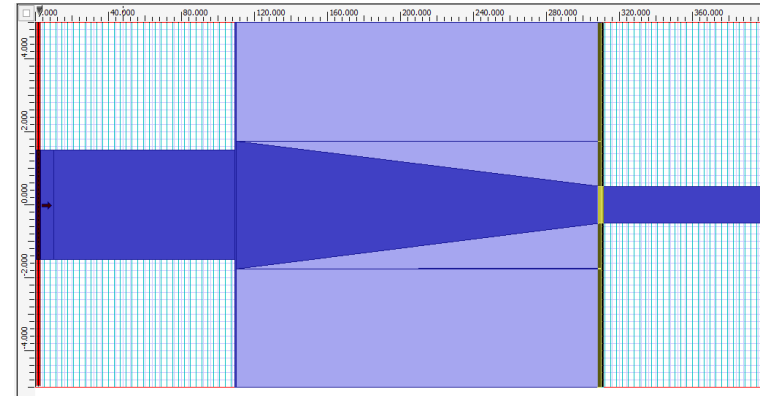


Waveguides in $[01\bar{1}]$

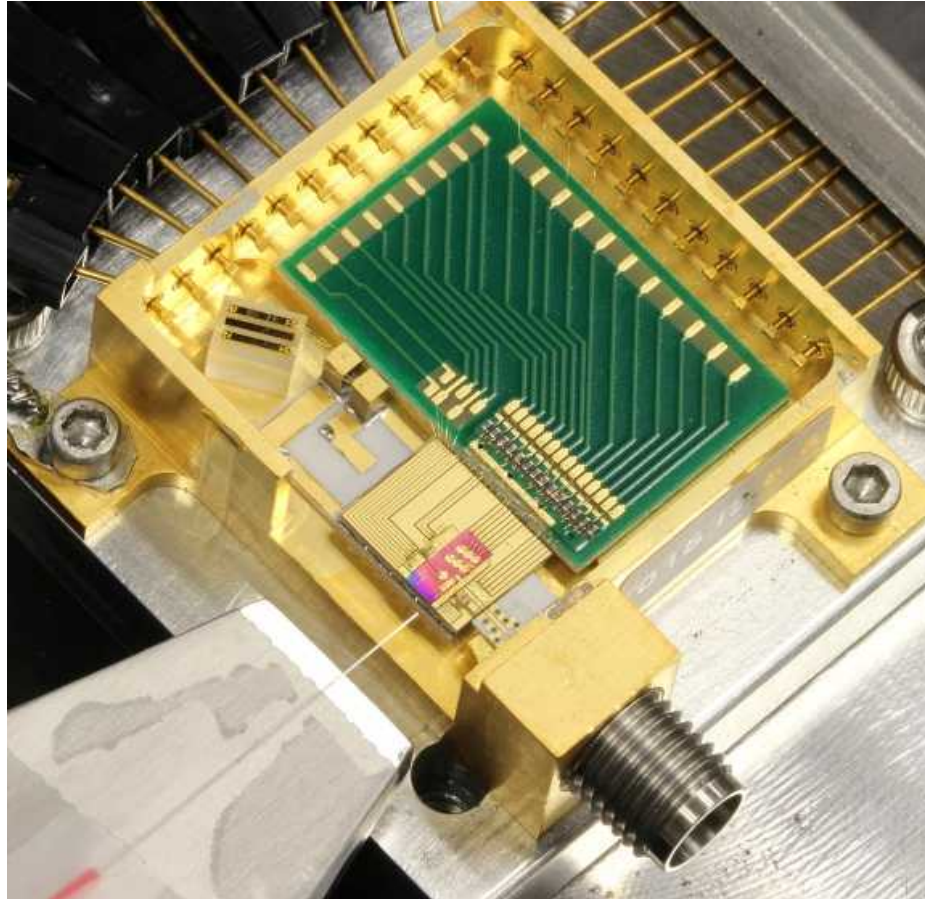


Ridge to Buried Heterostructure Coupler

- Laser and modulator has been optimized for ridge waveguide architecture
- Rings are optimized for buried heterostructure architecture
- Transition between the two waveguide types is done by tapering
- Experimental measurements show excess loss of 0.14 dB/transition
 - Theory predicts 0.11 dB/transition

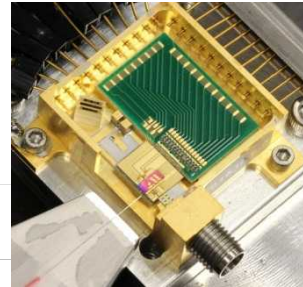
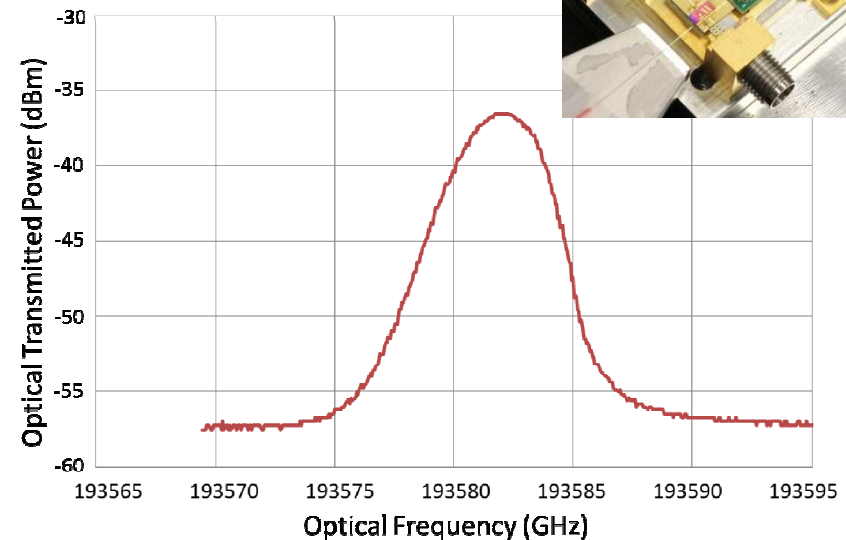
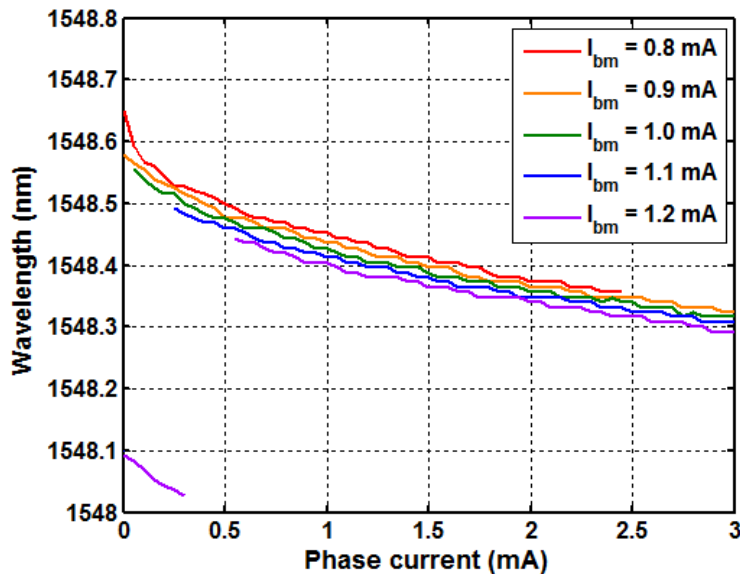


Characterization of Packaged Devices



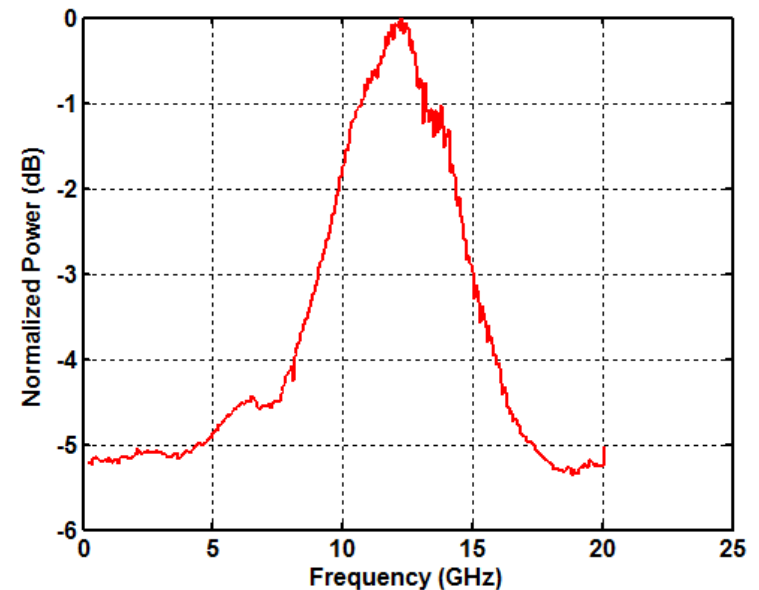
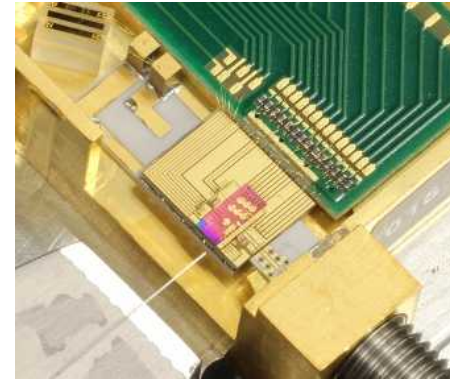
Characterization: Wavelength Scans

- Laser wavelength was scanned by adjusting phase current over a continuous tuning range
- Strong optical power gives the best measurement of filter shape
 - 3-dB optical passbands of 3.8 GHz demonstrated
 - 3-dB electrical passband of 3.36 GHz



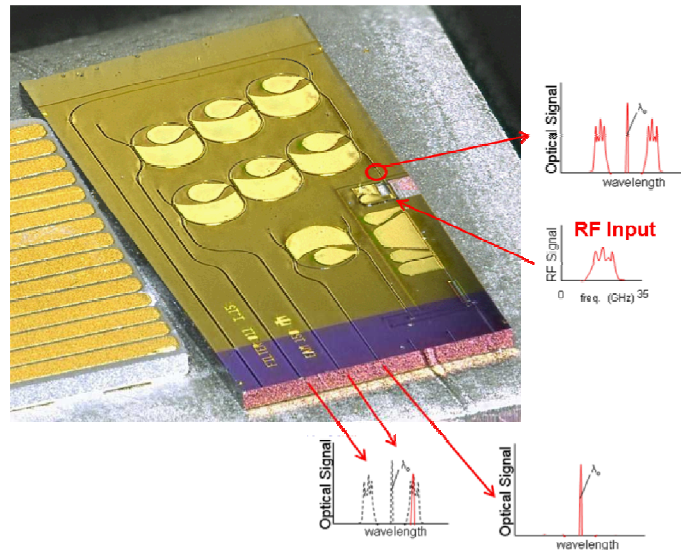
Characterization: RF Scan

- Sinusoidal signal was applied to modulator to create a sideband
 - The signal frequency was swept to sweep the sideband through the channelizing filter
- The lower signal power from the RF sideband is on the order of this noise
- Lower filter extinction is due to the filter noise floor
 - ASE from SOAs create a noise floor



Summary

- Demonstrated viable approach for optical RF channelizing PIC
 - Active 3-pole ring resonator filters
 - >20 dB of optical extinction
 - State-of-the-art 4 GHz passband matching models
 - Further reduction in passband possible with new designs
 - Lower crosstalk can be achieved with higher pole-filter
 - Demonstrated filtering of RF signal
 - Performance limited by SOA noise and sideband power
 - Improvements in modulator efficiency will improve signal to noise
 - Traveling wave modulators
 - Mach-Zehnder modulators





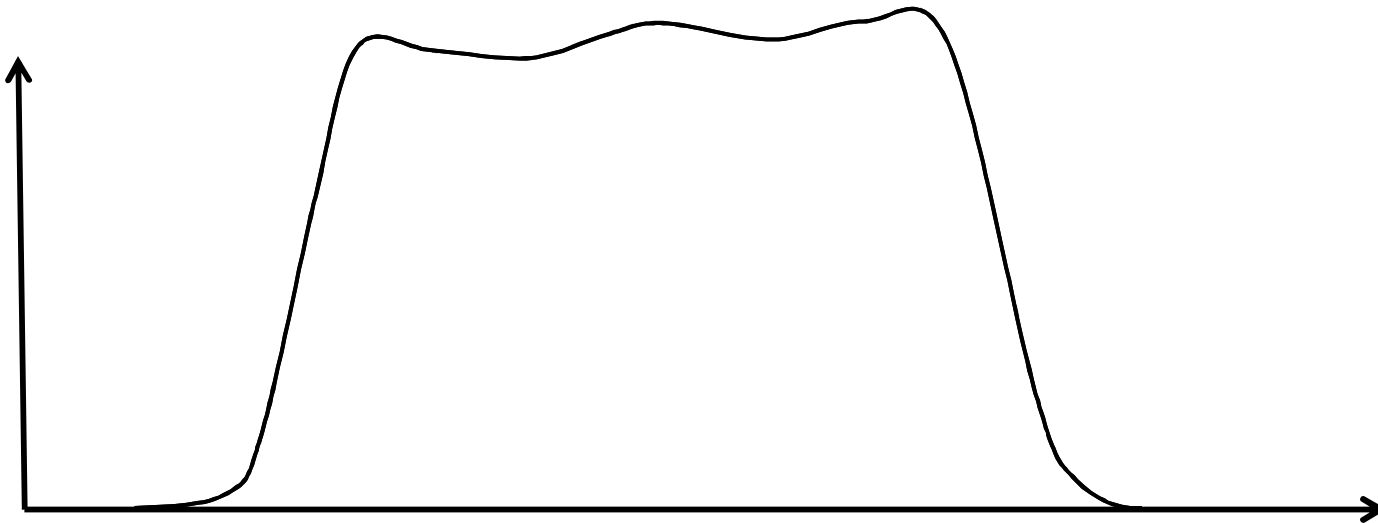


Backup Slides



Motivation

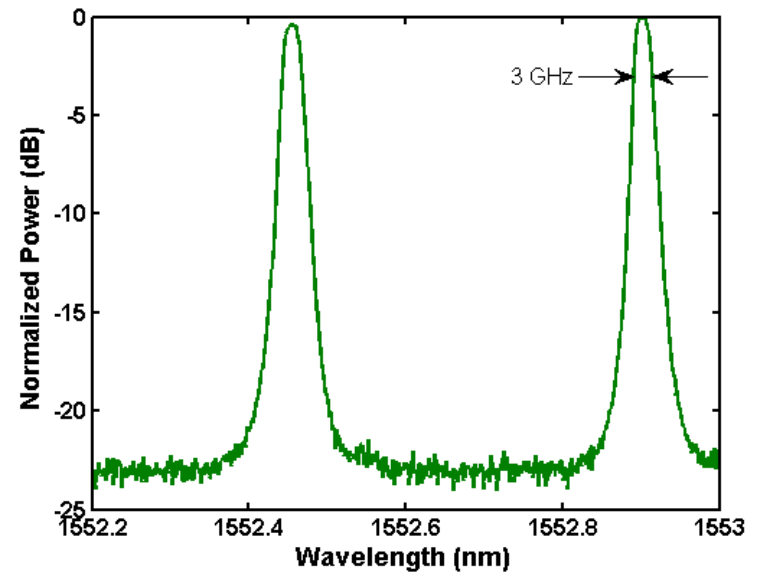
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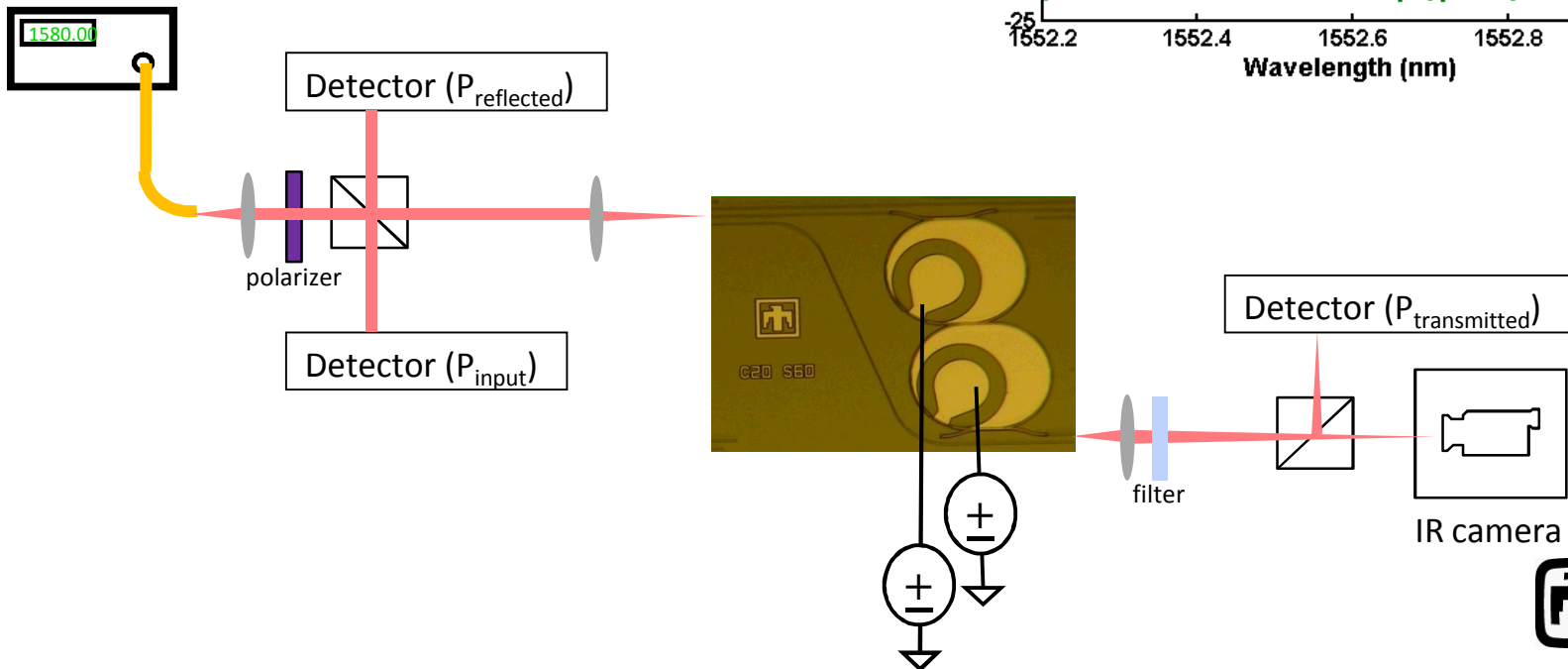
Experimental results

- Scanning source measurement

- Wavelength swept on a tunable laser source
- 12 nm filter added to the ring output
 - This filters out much of the ASE from the SOA
- 3 GHz 3-dB optical bandwidth
- Quality factor of 65,000

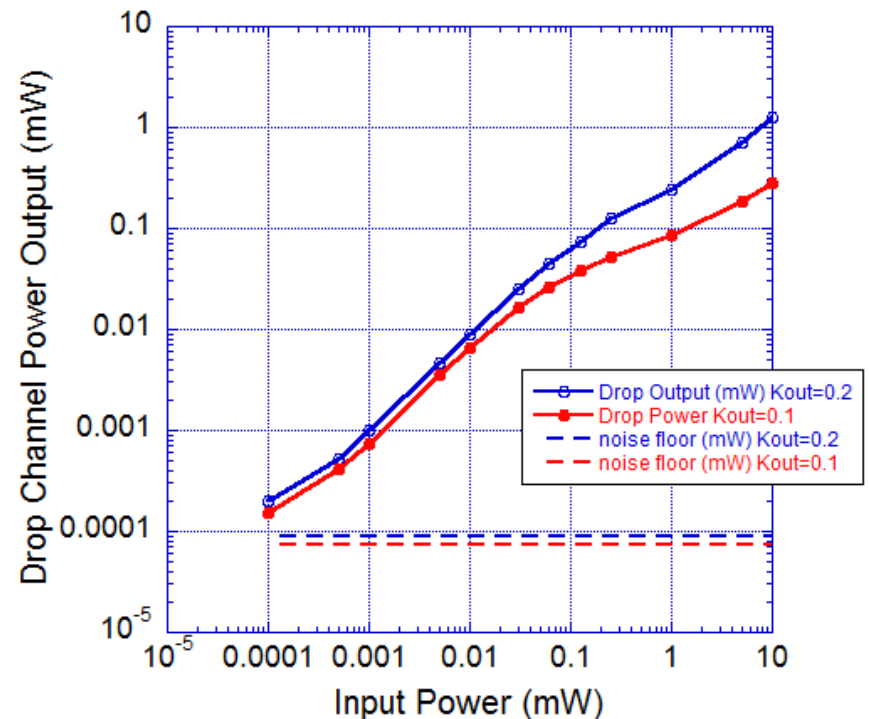
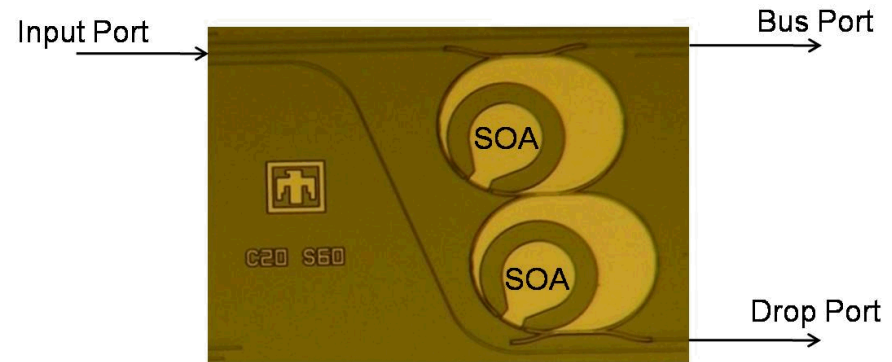


Tunable Laser



Previous Work

- Dual ring resonators with quality factor of 65,000
 - Linewidth of 3 GHz
- Analysis of dynamic range of active ring resonator filters
 - Active ring resonator filters can offer improved performance over passive filters (SiON) due to no coupling losses
 - Limitations due to amplified spontaneous emission and SOA saturation must be designed in

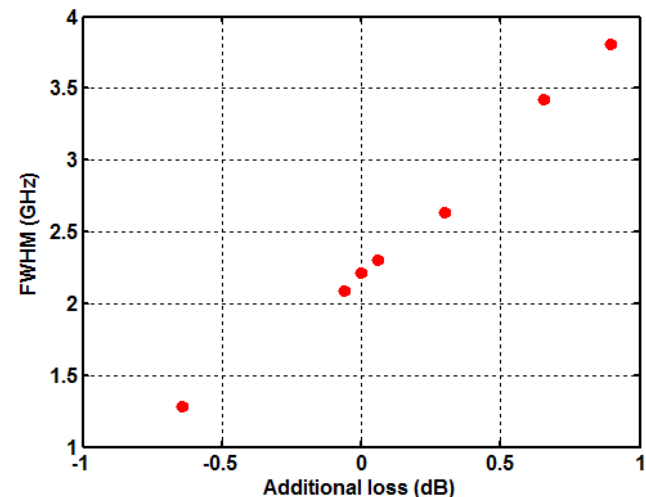
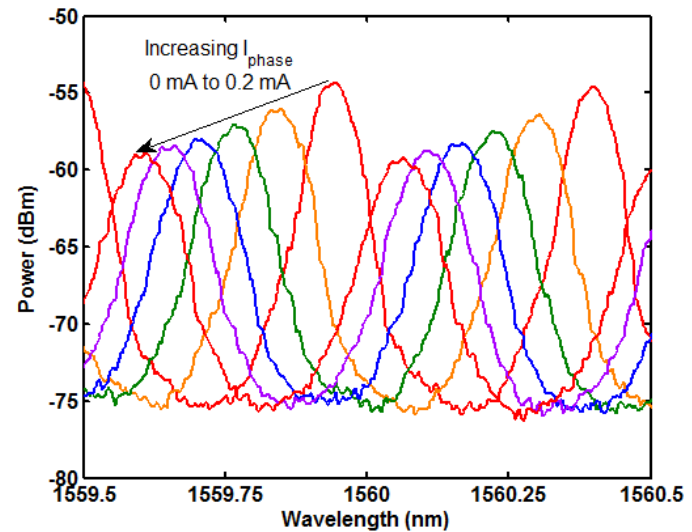


“Cascaded Double Ring Resonator Filter with Integrated SOAs”, OFC 2011

“Wide Dynamic Range of Ring Resonator Channel-Dropping Filters with Integrated SOAs”, OFC 2011

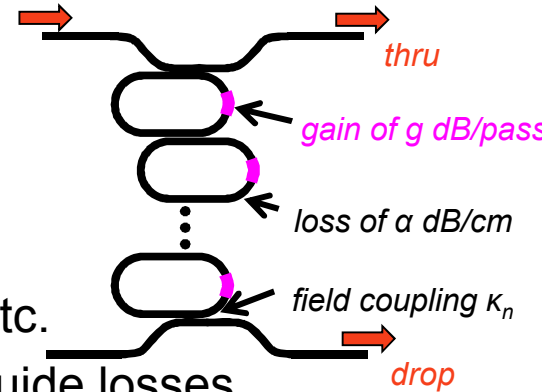
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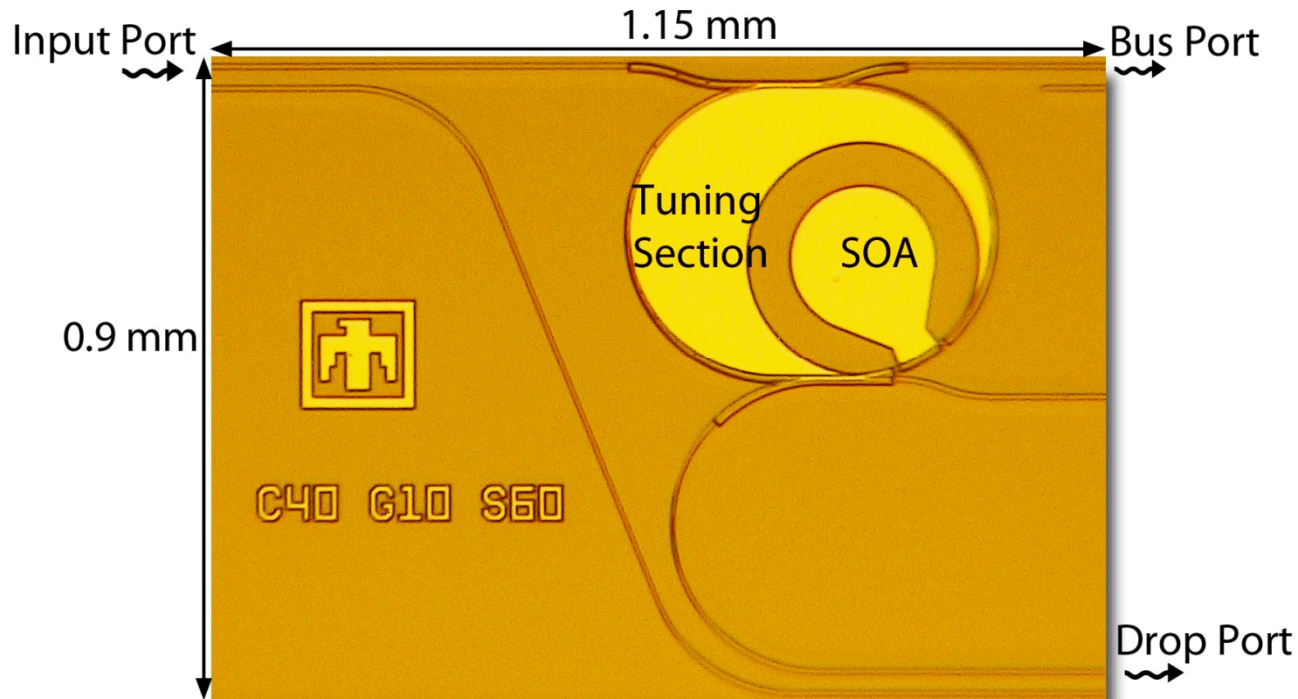


Design of Active Ring Filters

- Active ring resonators offer:
 - Compact size
 - Low, or zero, back reflection
 - Monolithic integration with lasers, modulators, SOA, etc.
 - Gain elements can be used to compensate for waveguide losses
 - Design Considerations:
 - Bandwidth determined by:
 - Coupler strength and optical loss
 - Filter profile defined by:
 - Coupler strengths and number of rings and internal net loss
 - Extinction ratio influenced by:
 - Noise from optical amplifiers and optical loss
 - Tunability affected by:
 - Size of tuning section and induced loss
- Loss, couplers, and optical gain needs to be tightly controlled



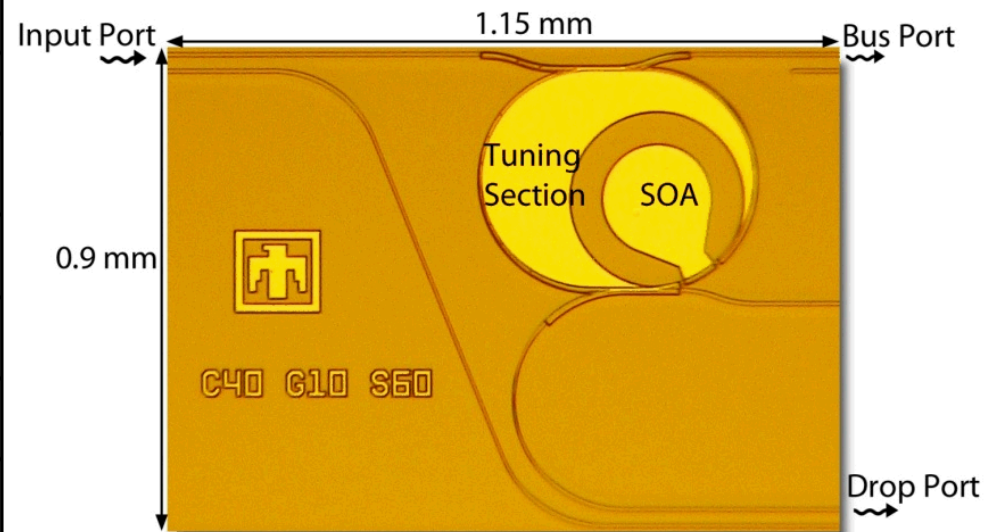
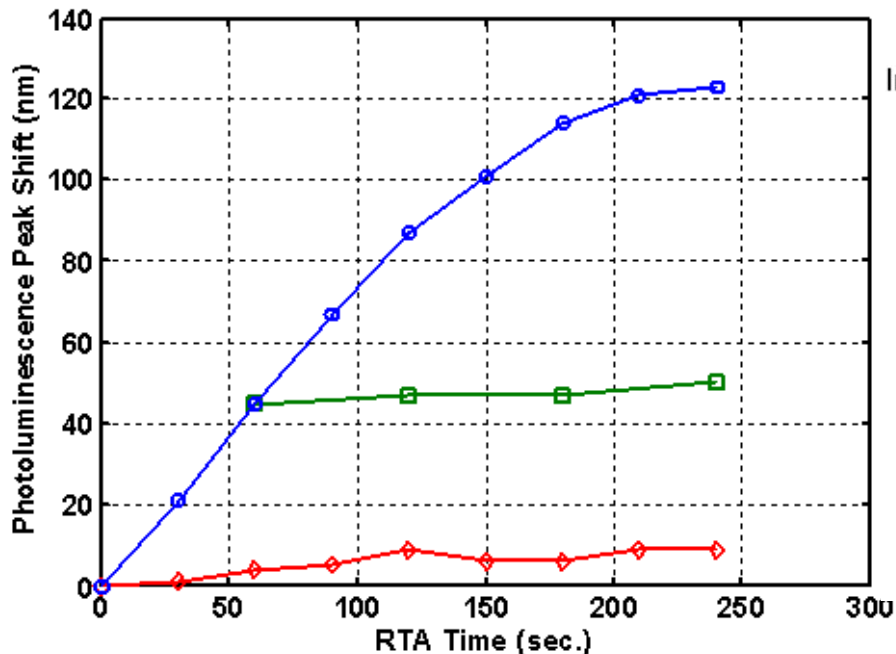
Approach



- Couplers designed for 1-2 GHz linewidth
 - Fractional coupling power of 6% for both couplers
- Integrated 60- μm -long SOAs in the ring
 - Minimize loss through filter
 - Length and total gain designed for low noise
- Tuning section
 - Current injection

Monolithic Integration Platform

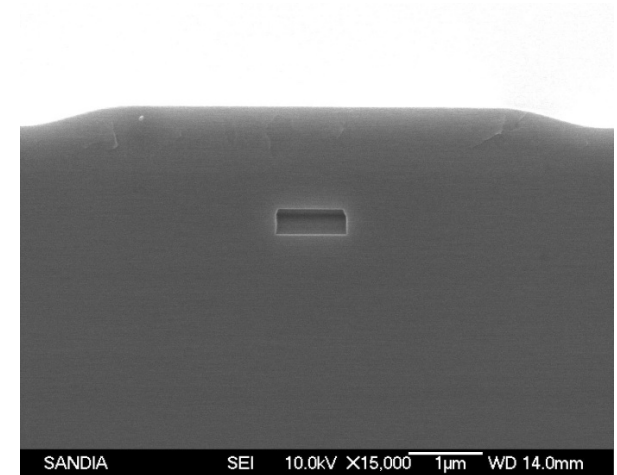
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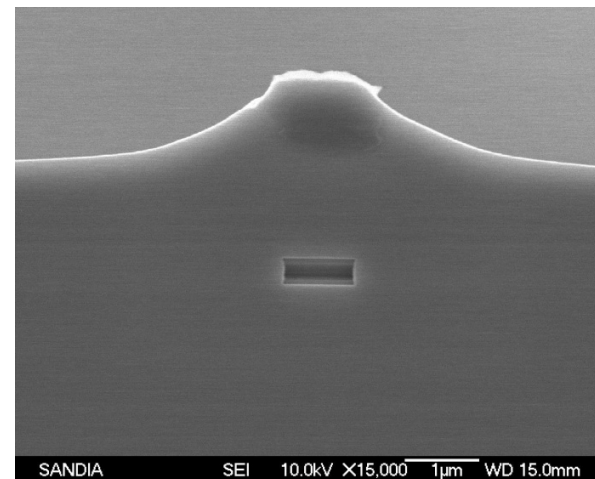
Buried Heterostucture Waveguides

- Waveguide definition process
 - Stepper lithography
 - 0.6 μm resolution
 - Dry etch
 - MOCVD Regrowth
 - InP cladding
 - InGaAs contact layer
- Buried heterostucture advantages
 - Waveguide thickness defined by epitaxial material
 - Semiconductor etch only defines guiding width and coupler gap
 - Devices are essentially not affected by variations in etch depth

Waveguides in [011]



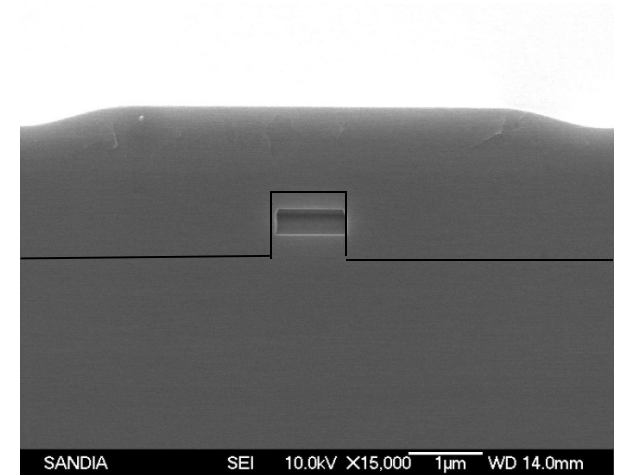
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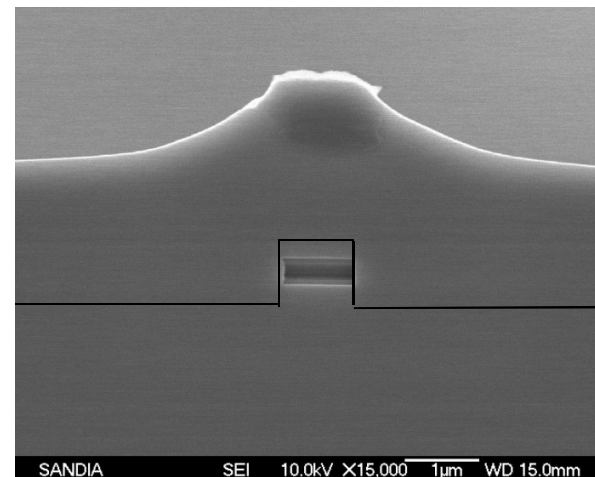
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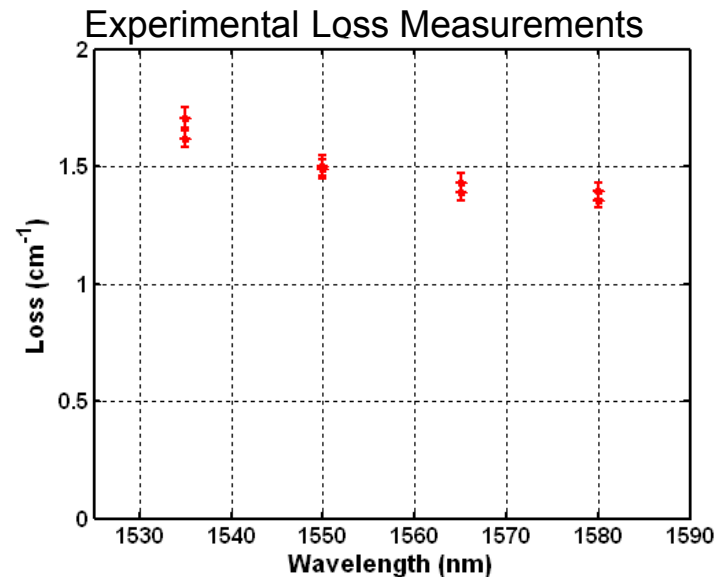
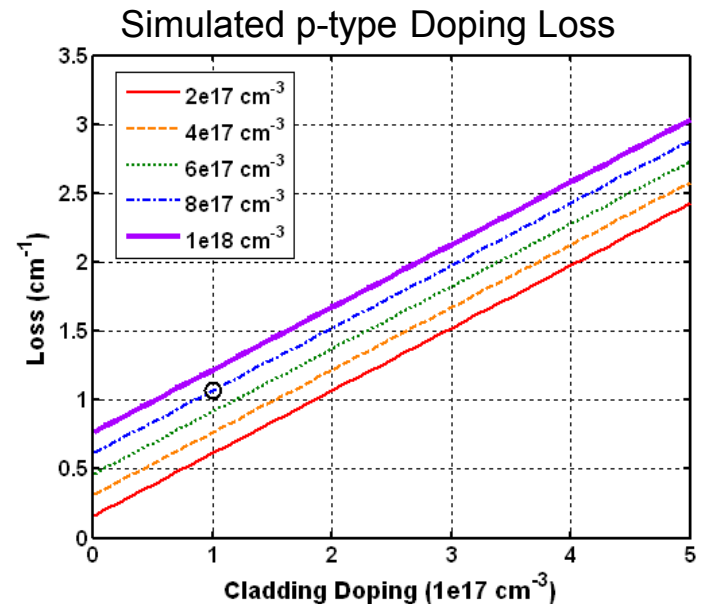


Waveguides in $[01\bar{1}]$



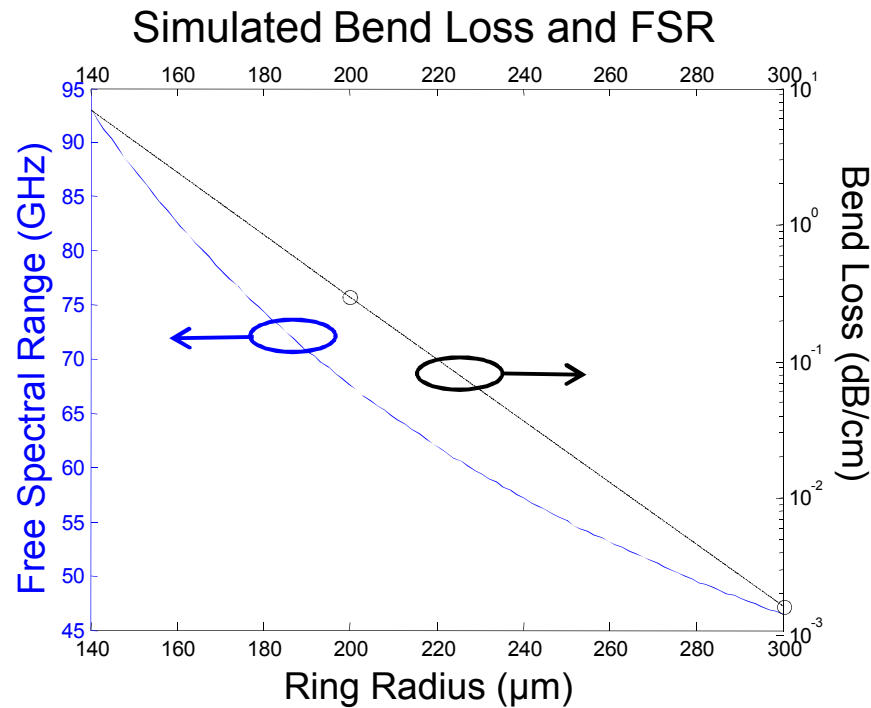
Low Loss Waveguides

- Low loss waveguides
 - Loss and coupling define the bandwidth of the filter
- Scattering and Absorption Loss
 - Modal overlap with InP p-type doping regions is a major source of loss
 - 500 Å doping spike at the regrowth interface
 - Compensates for Si contamination at the regrowth interface
 - Doping of the regrown p-type cladding
 - Waveguide loss was measured using Fabry-Perot cavity measurements
 - 1.5 cm^{-1} at 1550 nm



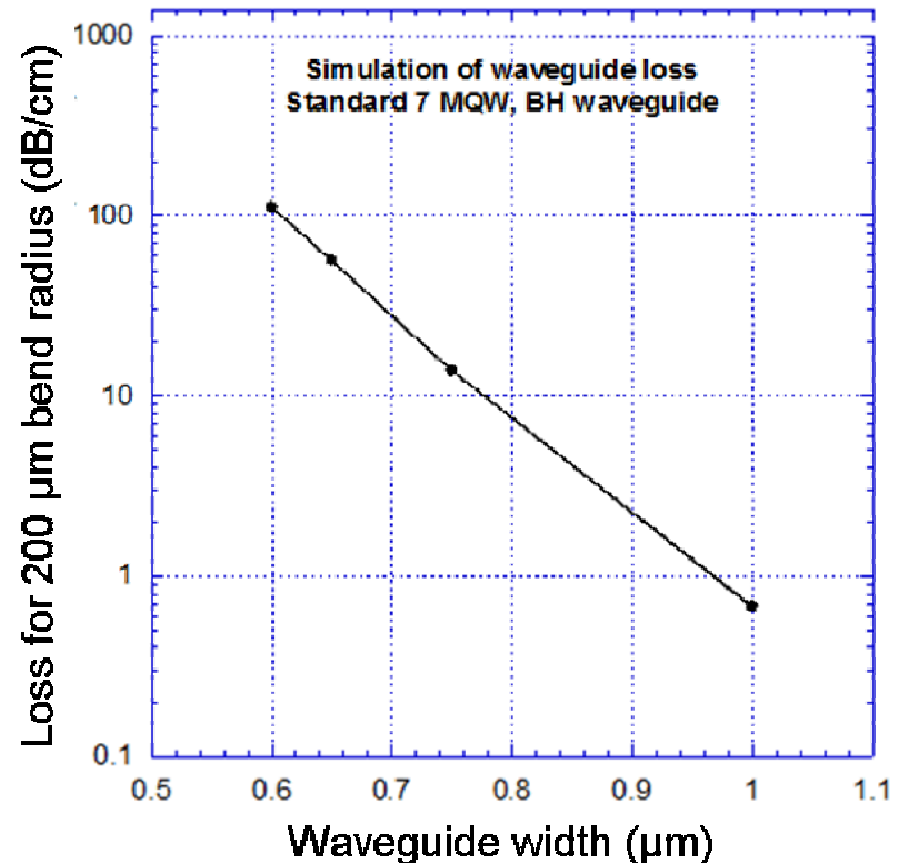
Low Loss Waveguides: Bend Loss

- Low loss waveguides
 - Loss and coupling define the bandwidth of the filter
 - Output coupling and waveguide loss
- Bend loss
 - Tradeoff between loss and FSR
 - 200 μm radius for 1 μm waveguide width



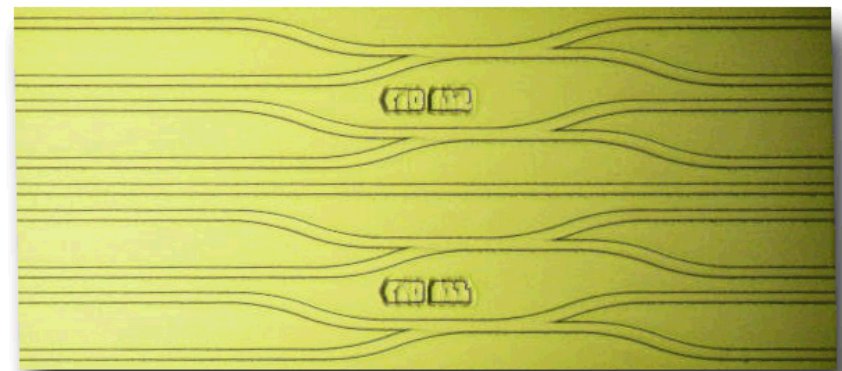
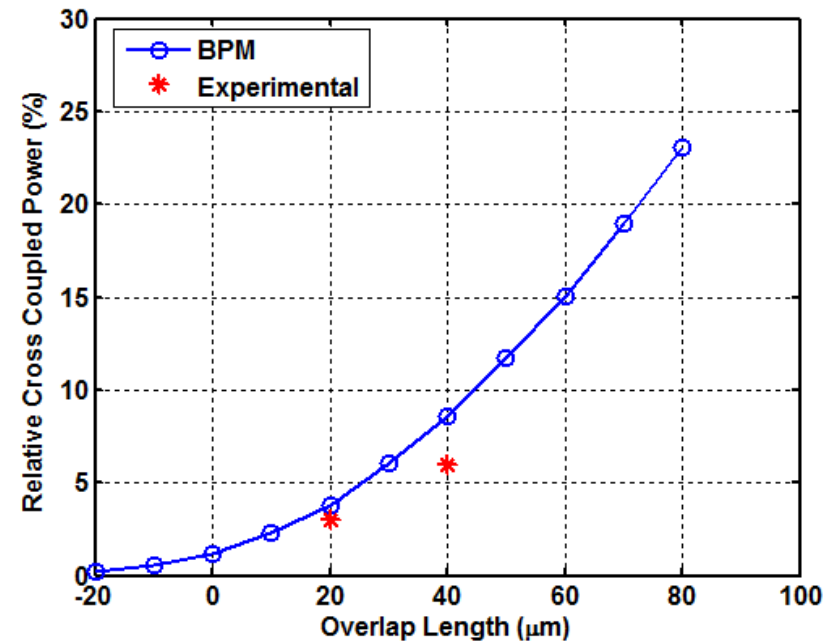
Low Loss Waveguides: Bend Loss

- Waveguide width is very important to bend loss
- Lithographic bias can significantly affect bend losses
 - Projection lithography/stepper used
 - Dimensions verified by CD SEM measurements
 - Monitors bias drift over time
 - Done before waveguide etch allowing for rework.



Couplers

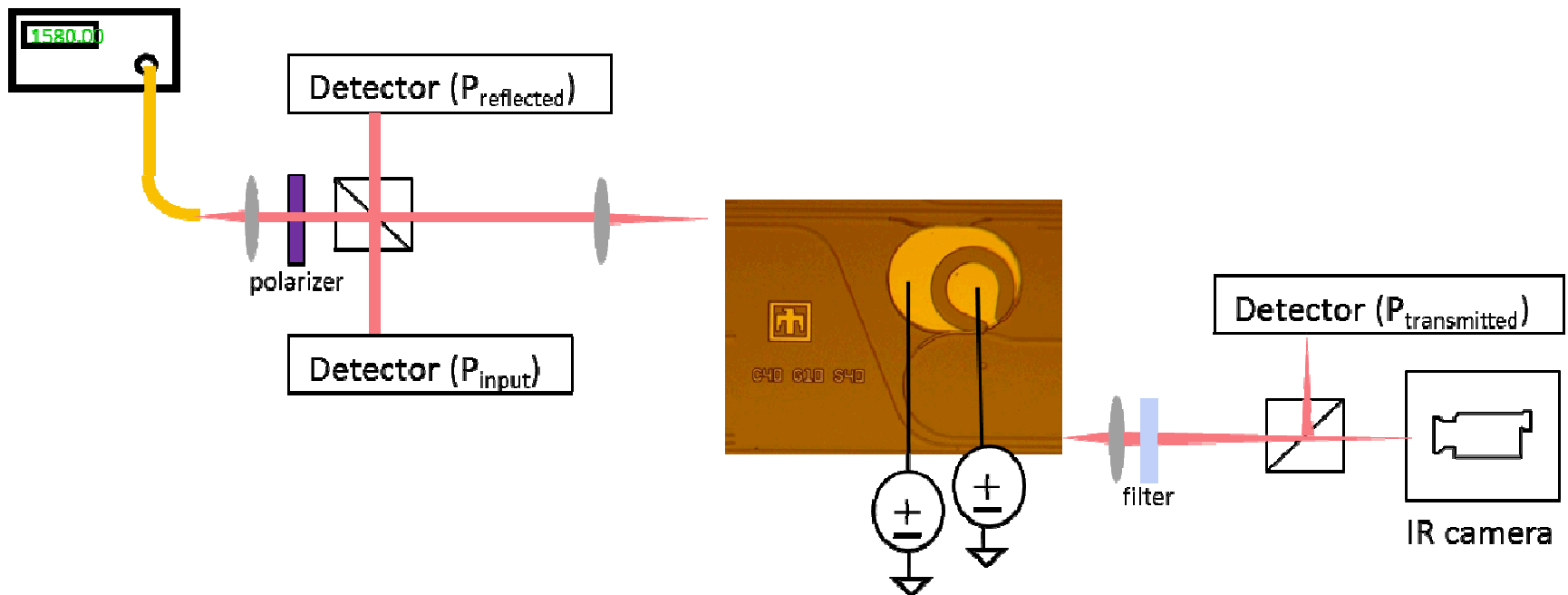
- Coupler design
 - Couplers utilize 1 μm waveguides with 1 μm gap
 - Coupling defined by length overlap region
 - Lithography biases are constant
 - Consistency in coupler values within and between process runs
- Simulations used to predict coupling
 - BPM simulation
 - Includes waveguide bends
 - Experiment shows lower coupling than predicted by BPM
 - Waveguide widths and gap has a bias due to fabrication



Experimental results

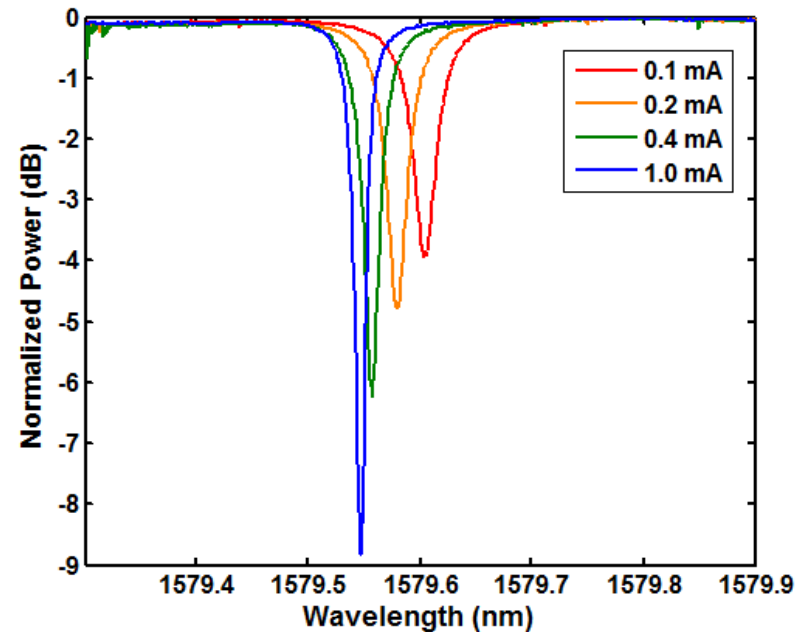
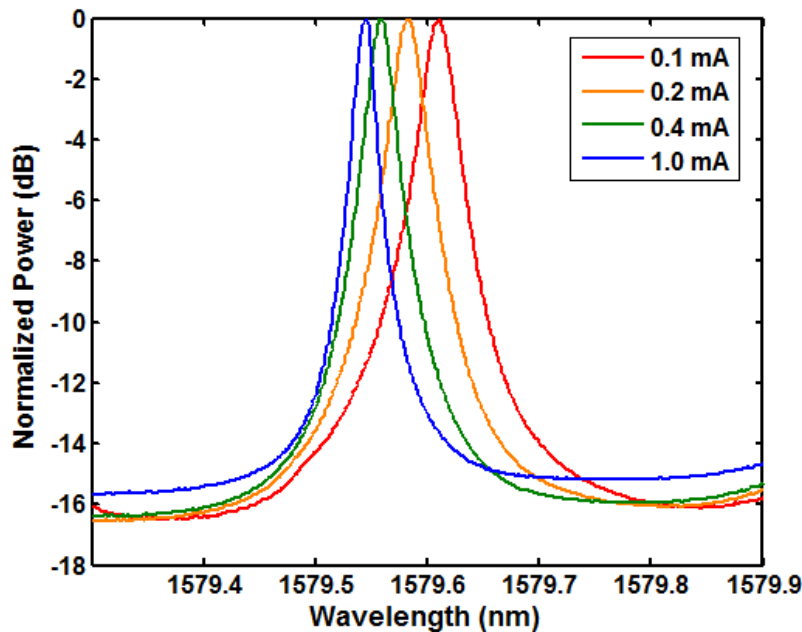
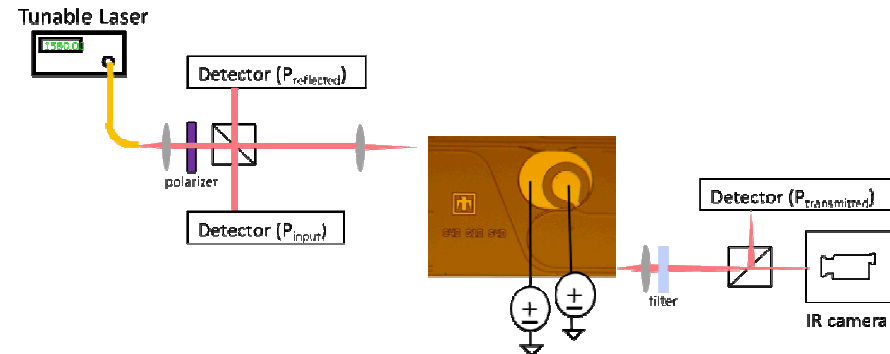
- Scanning source measurement
 - Wavelength swept on a tunable laser source
 - 12 nm filter added to the ring output
 - This filters out much of the amplified spontaneous emission (ASE) from the SOA

Tunable Laser



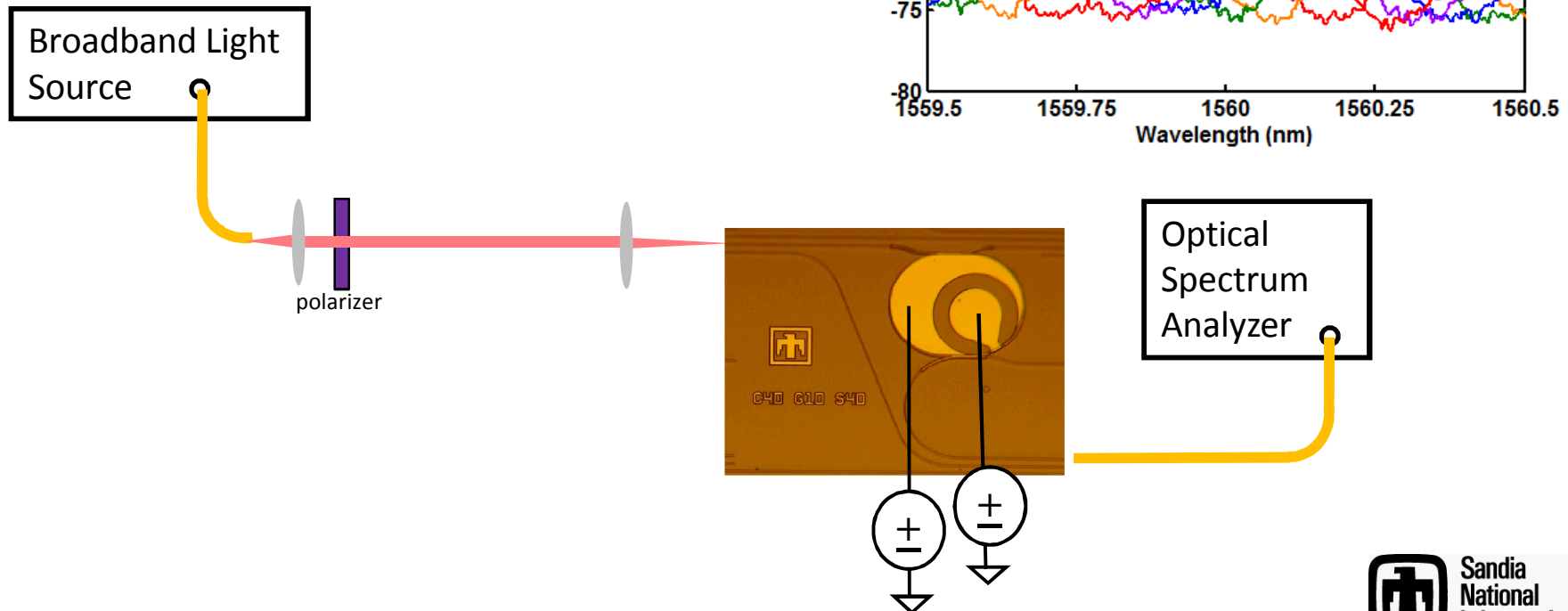
Experimental results

- Scanning source measurement
 - Variation in SOA current from 0.1-1.0 mA
 - >15 dB extinction
 - 3.5 GHz to 2.2 GHz FWHM optical linewidth



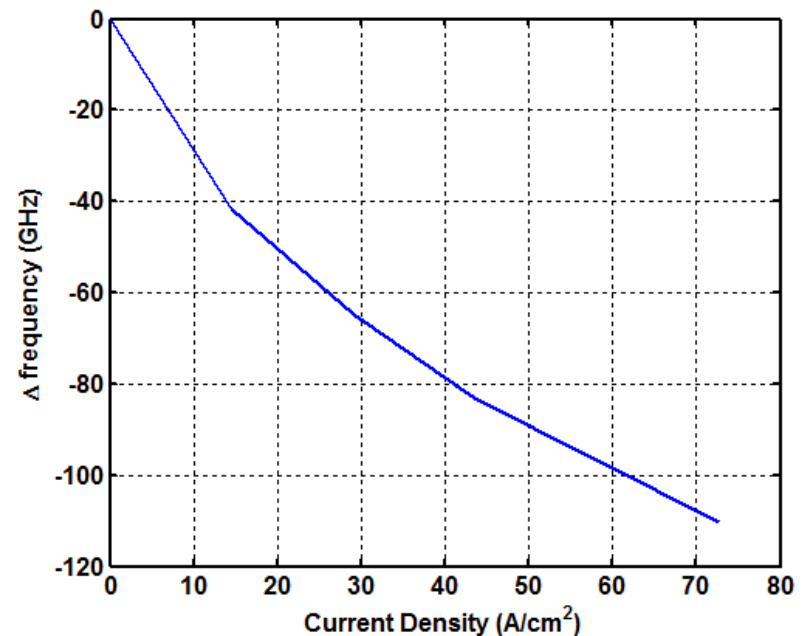
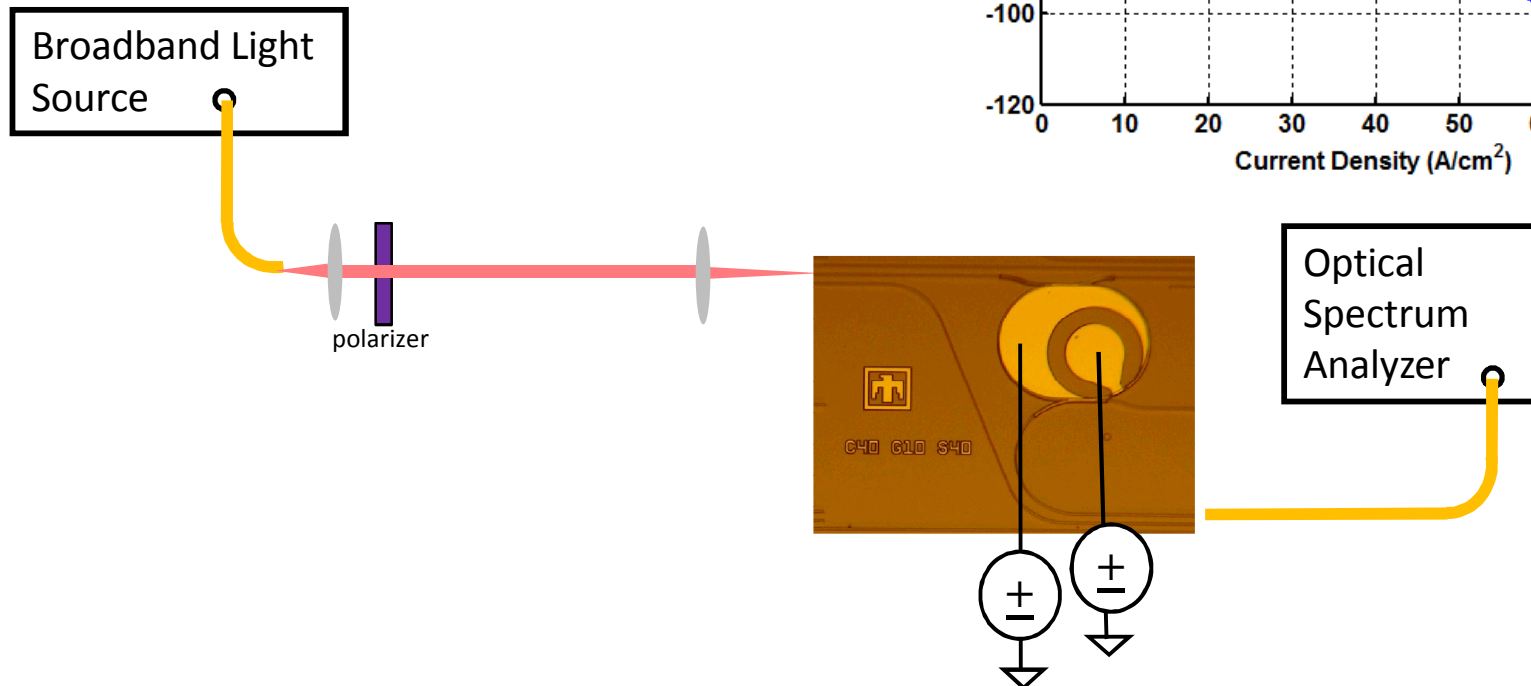
Experimental results

- Optical spectrum analyzer measurement
 - Broadband light source
 - Ring output fiber coupled to OSA
 - Better for larger wavelength scans
 - $I_{\text{SOA1}} = 2 \text{ mA}$
 - Extinction ratio of $>15 \text{ dB}$



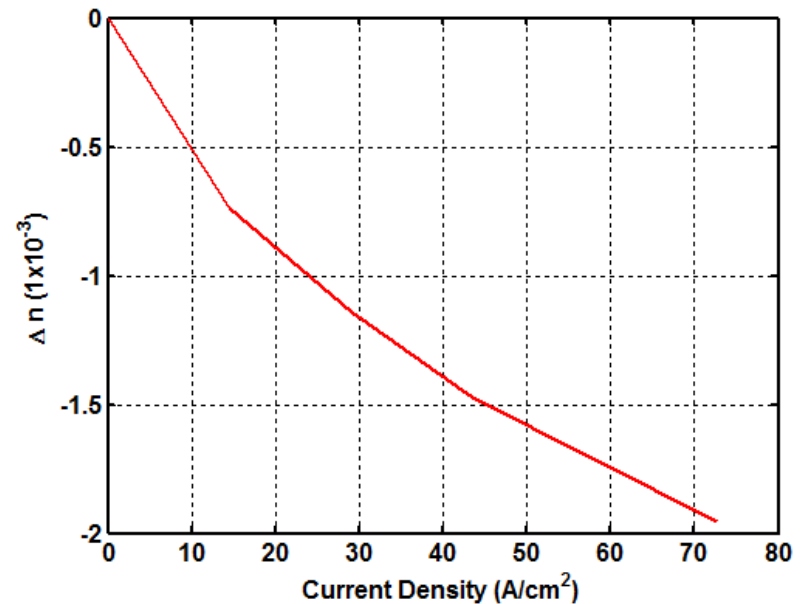
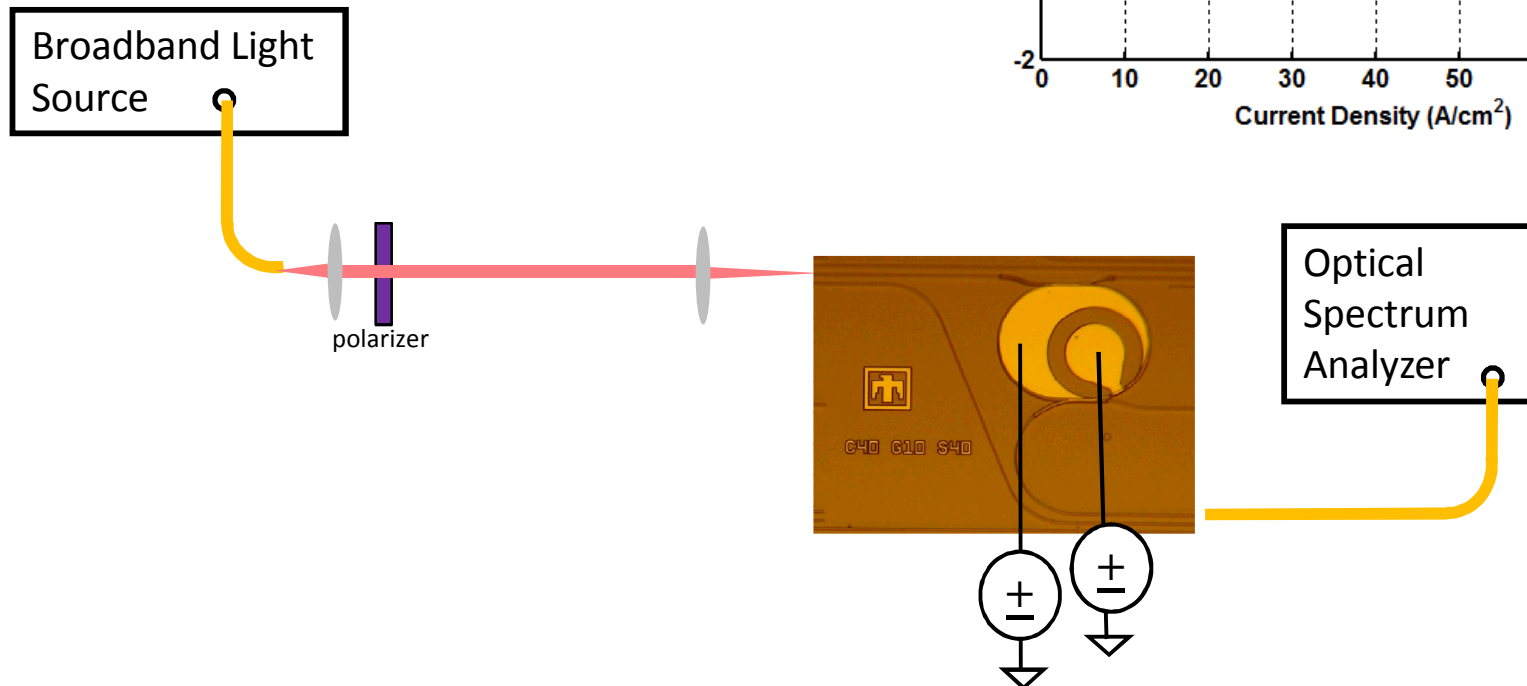
Experimental results

- Optical spectrum analyzer measurement
 - Broadband light source
 - Ring output fiber coupled to OSA
 - $I_{\text{SOA1}} = 2 \text{ mA}$
 - Extinction ratio of $>15 \text{ dB}$
 - 110 GHz with $I_{\text{Tune}} = 1 \text{ mA}$
 - Nearly twice the free spectral range

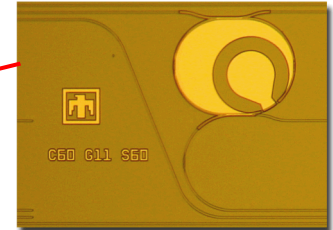
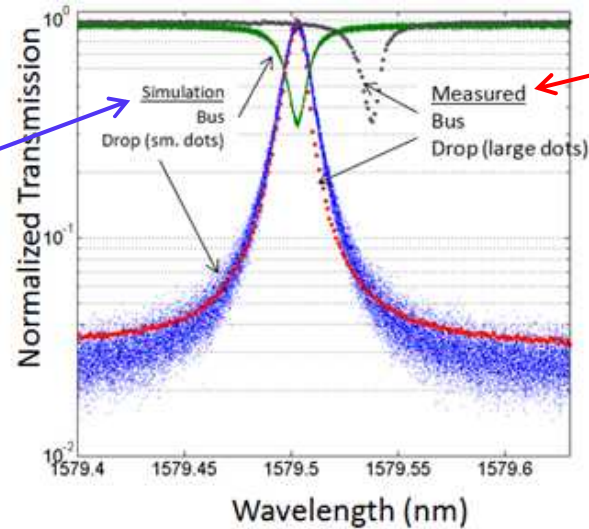
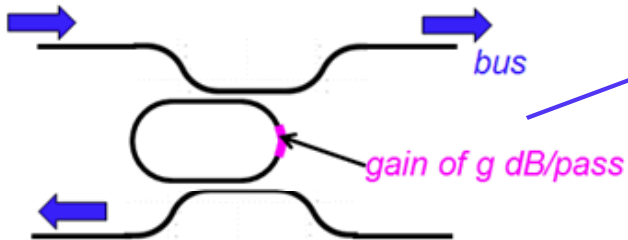


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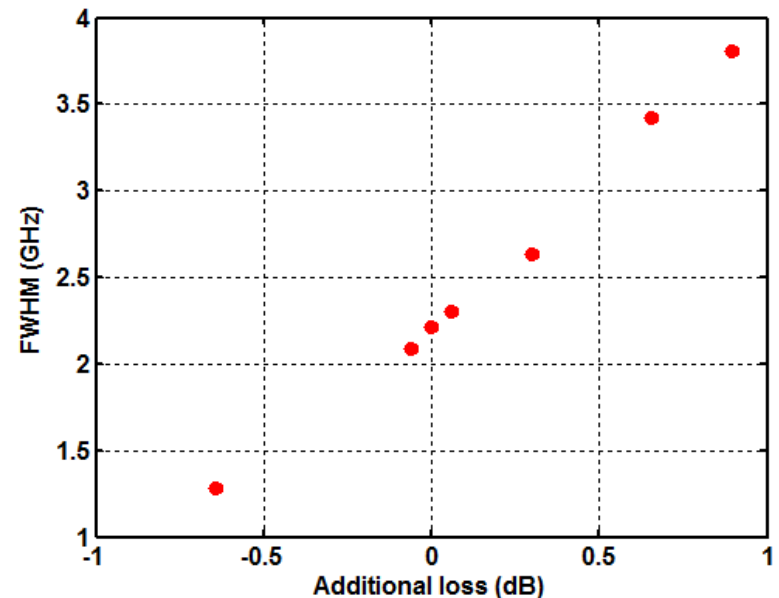
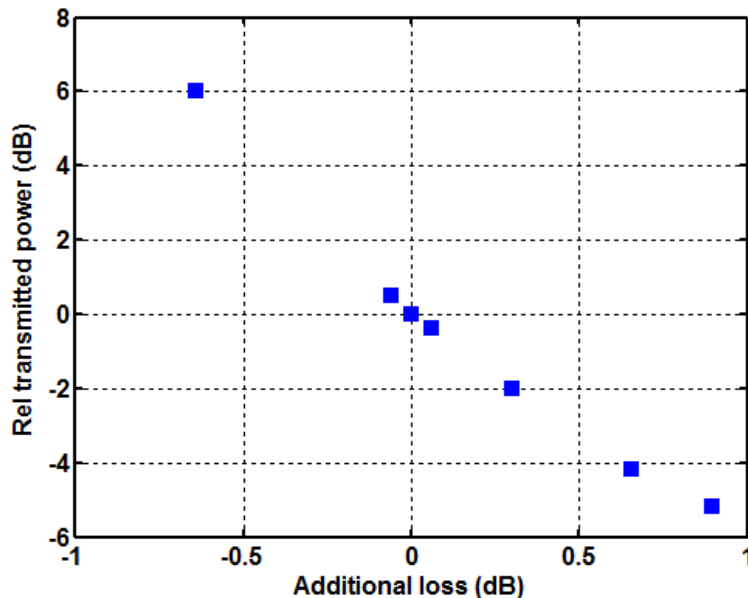
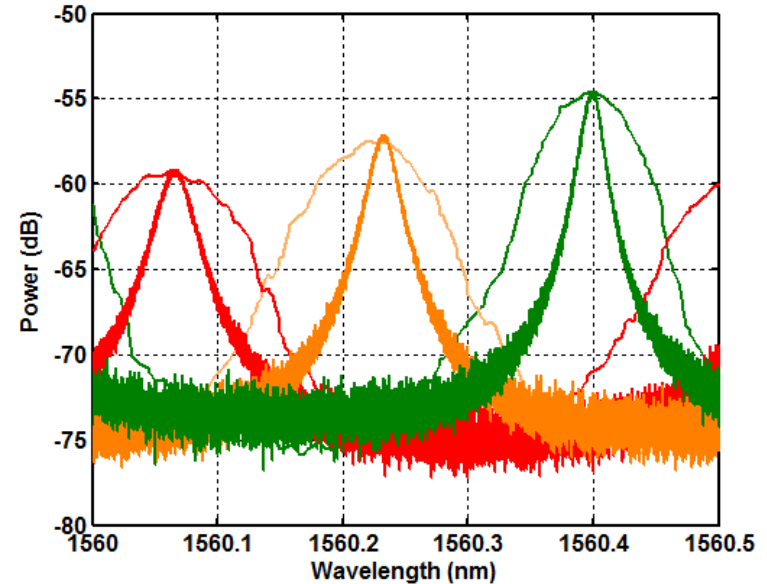
Simulation: Calibration



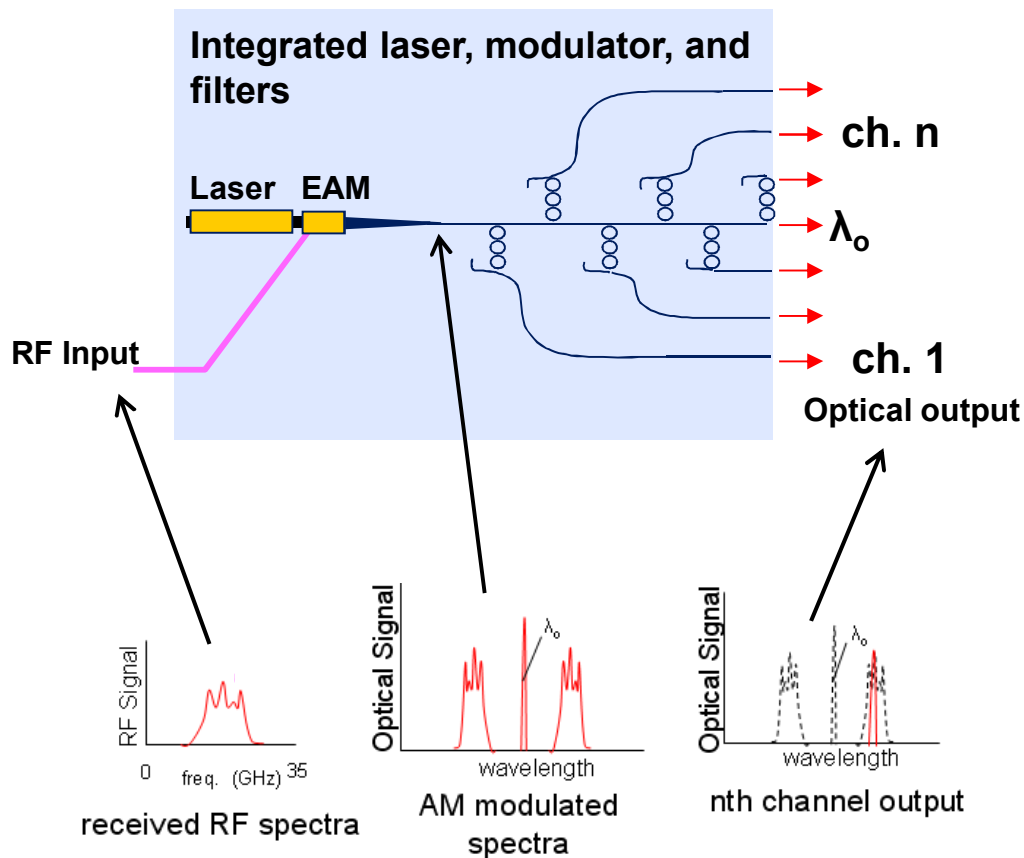
- Complete simulation of dynamic range and noise of active InGaAsP multi-ring filters
 - Include gain distortions and spontaneous emission noise
- Time dependent rate equation method
 - Gain and spontaneous emission modeled as function of injection current at all wavelengths simultaneously
- Fit experimental bandwidth of drop and extinction of bus to extract net round trip loss and coupling fraction
 - 6% coupler with 1.4 cm^{-1}

Simulation: Tuning Current Loss

- Tuning and loss from benchmarked from filter tuning data
- Effects of tuning induced loss on FWHM linewidth
- 0.9 dB of additional loss caused by tuning current
 - reduces peak power 5 dB
 - Increase FWHM by 1.6 GHz
- Loss can be compensated by increase in SOA gain

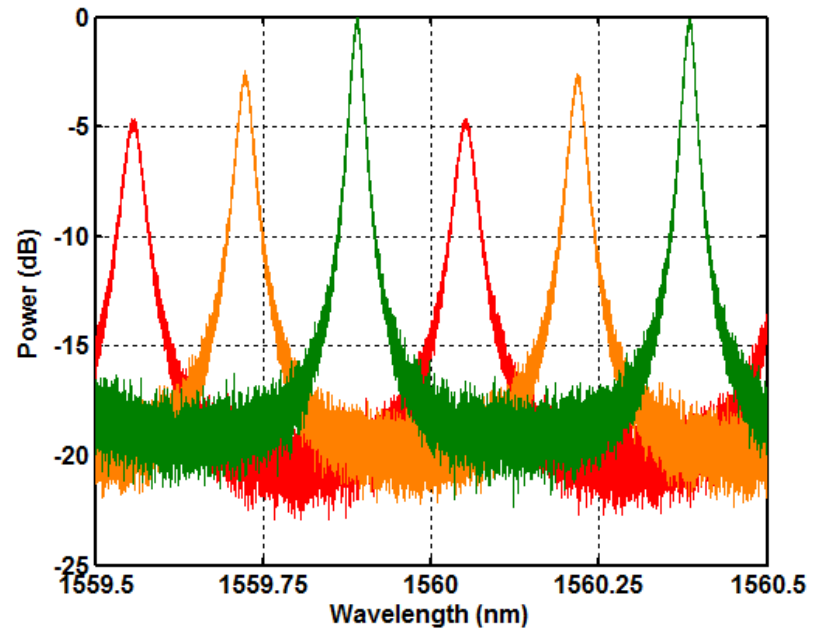


Motivation

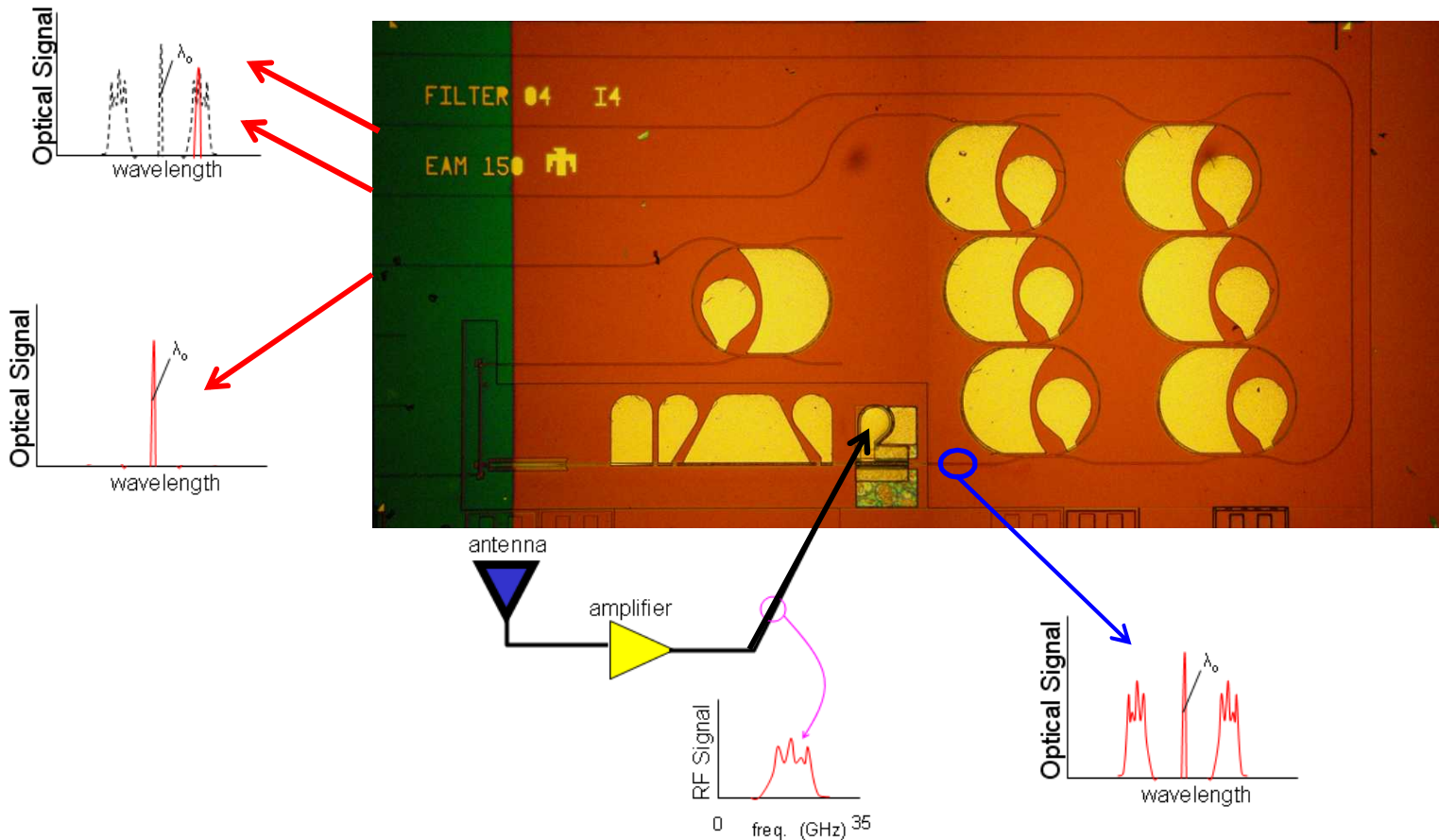


- Analyze an RF signal for frequency content
 - Filter outputs are spectral power density integrated over the filter bandwidth
- Monolithic integration with active components such as lasers and modulators enables compact, highly functional photonic integrated circuits (PICs)

Simulation benchmarking

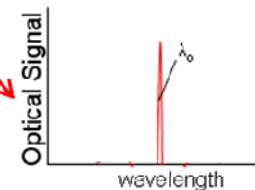
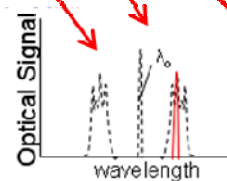
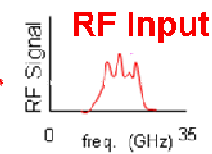
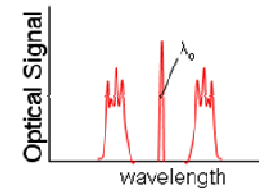
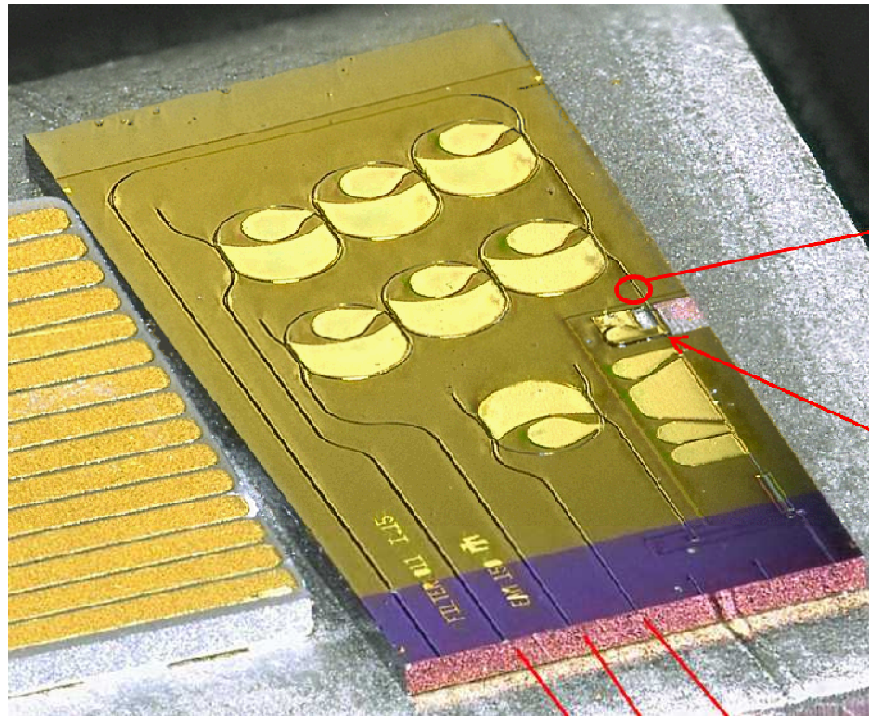


Monolithic RF Channelizing PIC



- Channelize RF signals for further analysis
- Monolithic integration enables compact, highly functional photonic integrated circuits (PICs)
- Tunable filters enable accurate placement across the frequency band

Monolithic RF Channelizing PIC

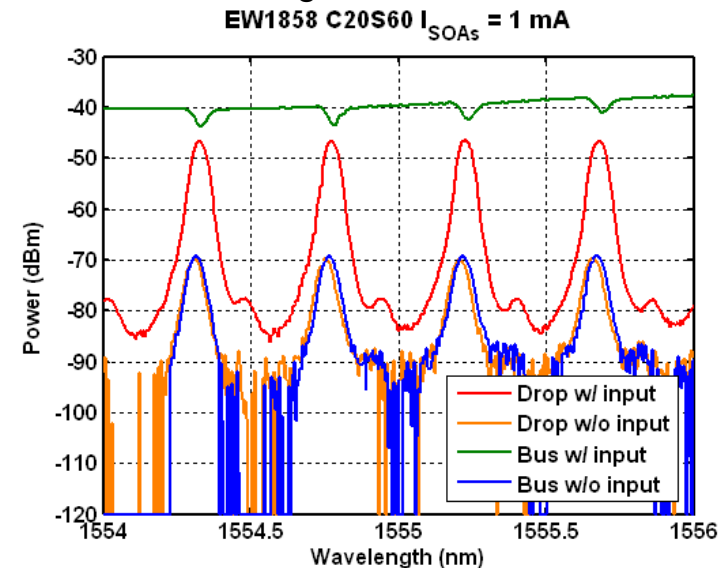


- Channelize RF signals for further analysis
- Monolithic integration enables compact, highly functional photonic integrated circuits (PICs)
- Tunable filters enable accurate placement across the frequency band

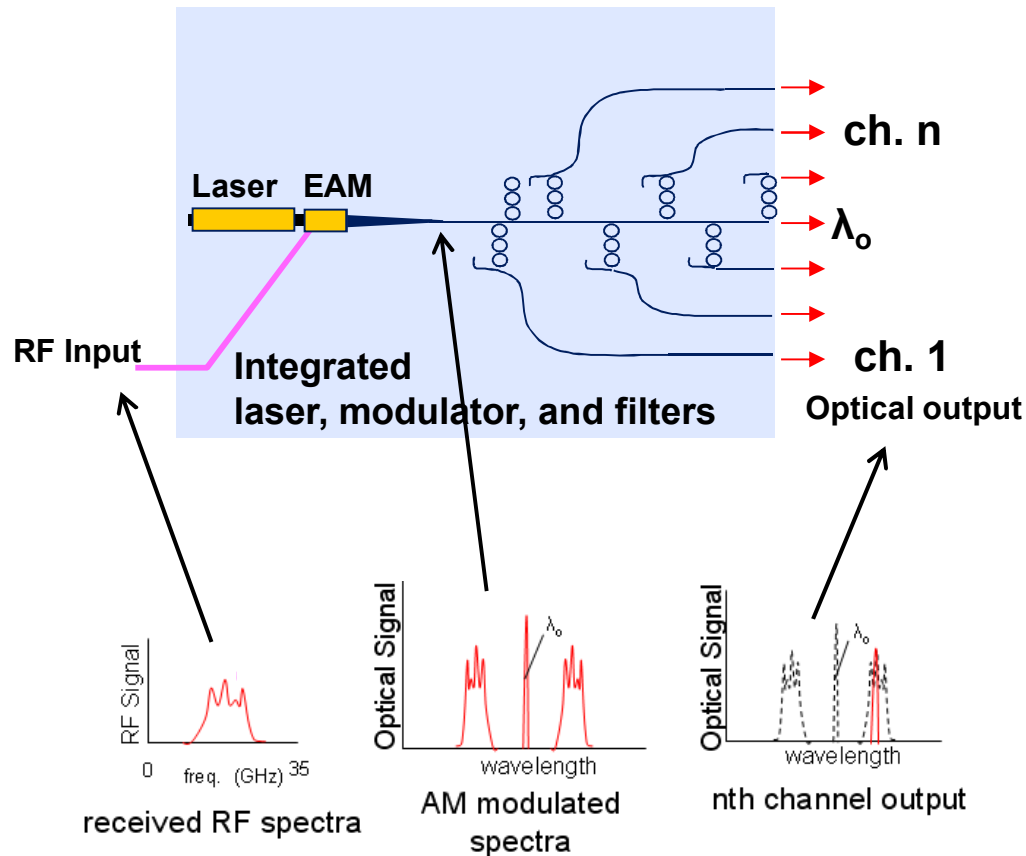
InP Active 2-ring Filter

need bigger font
on fig

- ASE source and OSA
 - Higher extinction
 - SOA-ASE goes is correct wavelength 'bin'
- Tunable laser and photodiode
 - Lower extinction
 - off resonance measurement includes SOA-ASE from all wavelengths
 - A filter (~ 5 nm) will give results similar to OSA
 - This can be external for testing
 - On a monolithic chip we need to add additional filtering

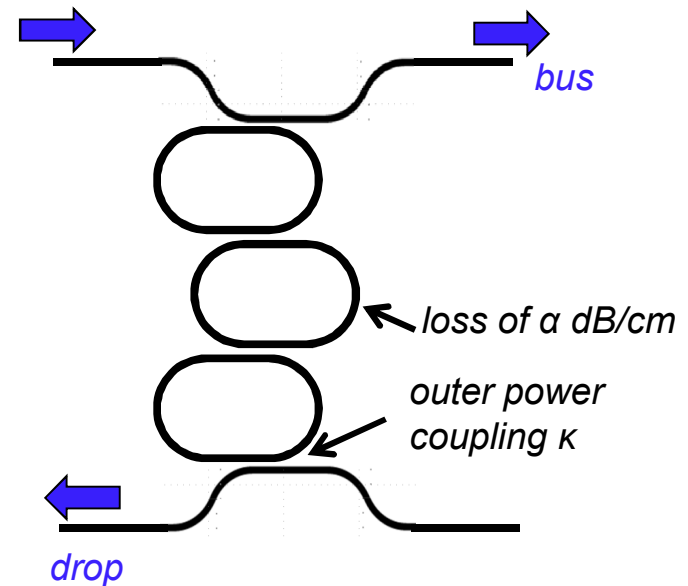
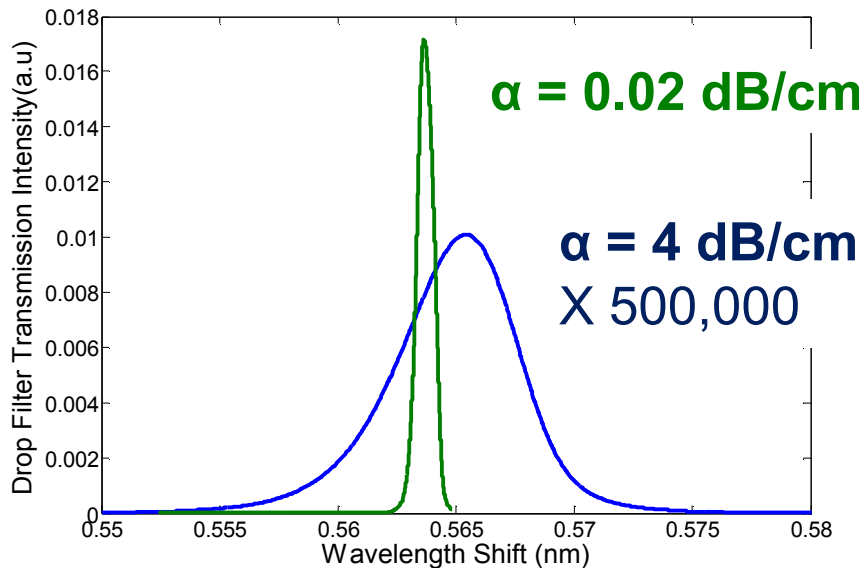


Channel-Dropping Filters

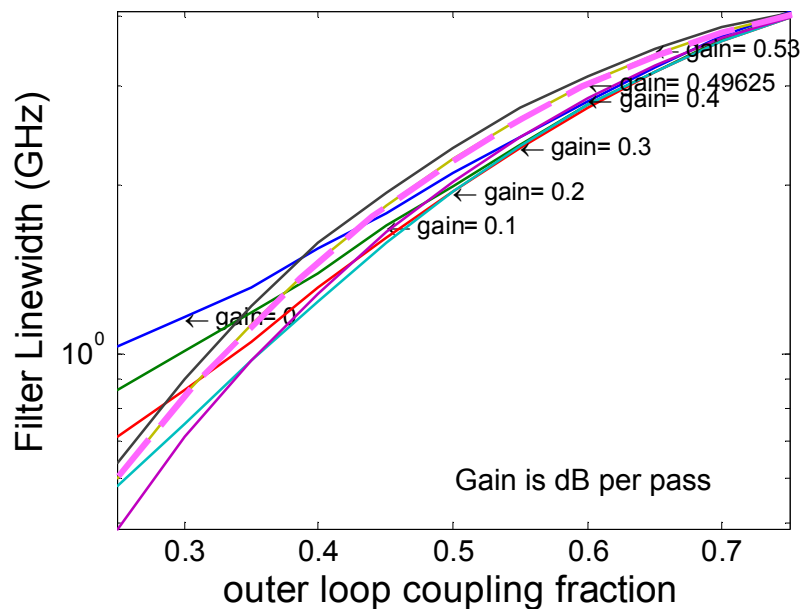
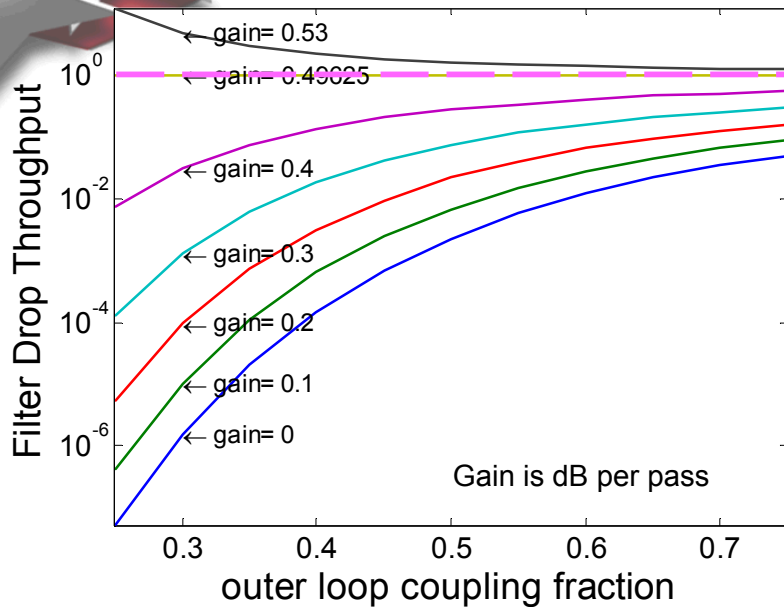


- Analyze an RF signal for frequency content
 - Filter outputs are spectral power density integrated over the filter bandwidth
- Monolithic integration with active components such as lasers and modulators enables compact, highly functional photonic integrated circuits (PICs)

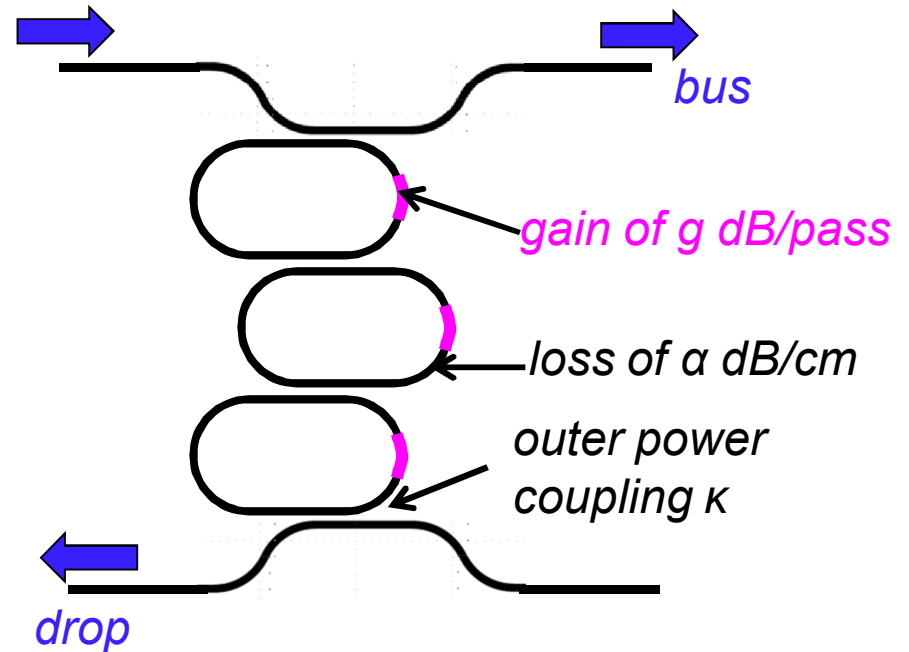
Monolithic Integration and Loss-Limited Filter Response



- Optical waveguide losses dominate the filter performance
- Useful passive ring resonant filters are typically made of glasses or undoped semiconductors with very low optical loss.
- Ring Filters with losses commonly seen in doped InGaAsP waveguides for active PICs have too little optical transmission to be useful as GHz-class filters



A Small Amount of Gain Offsets Losses

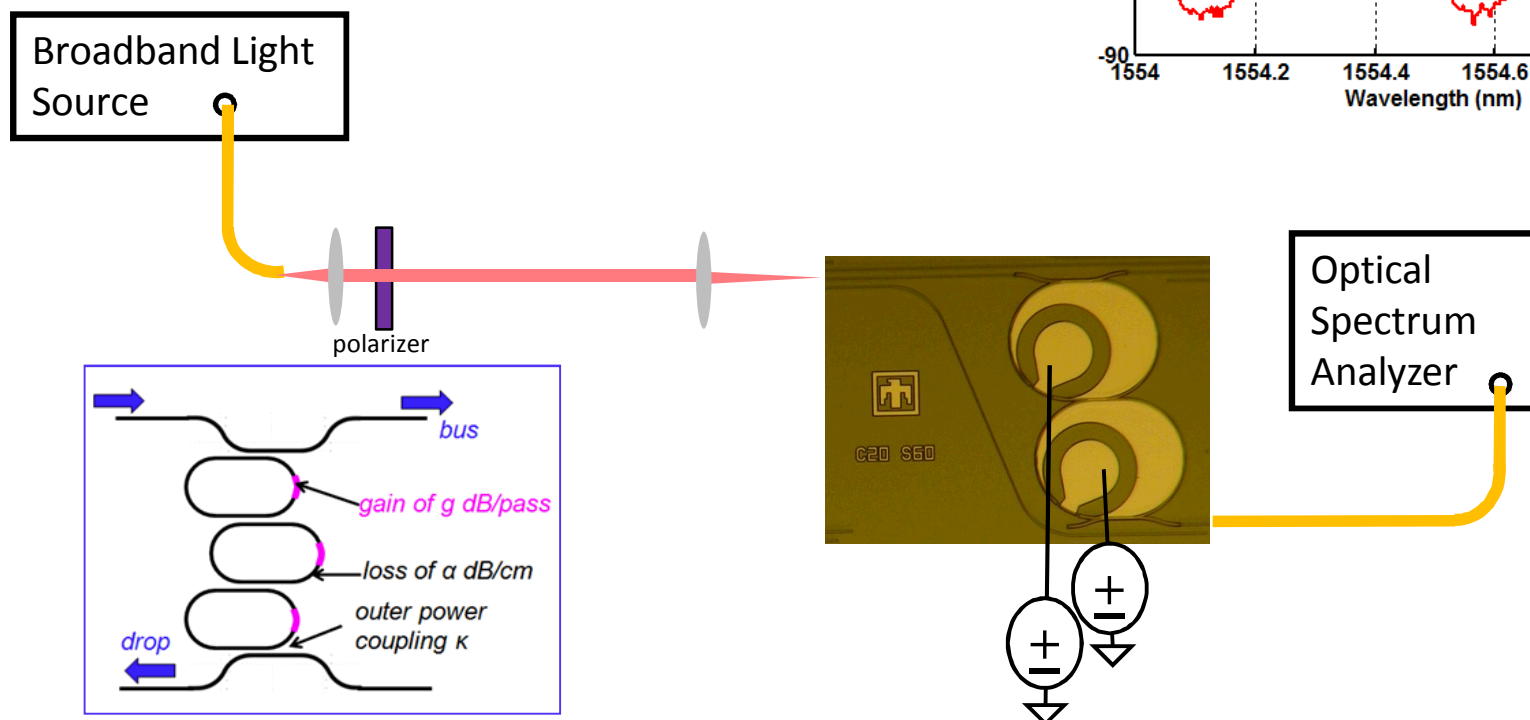
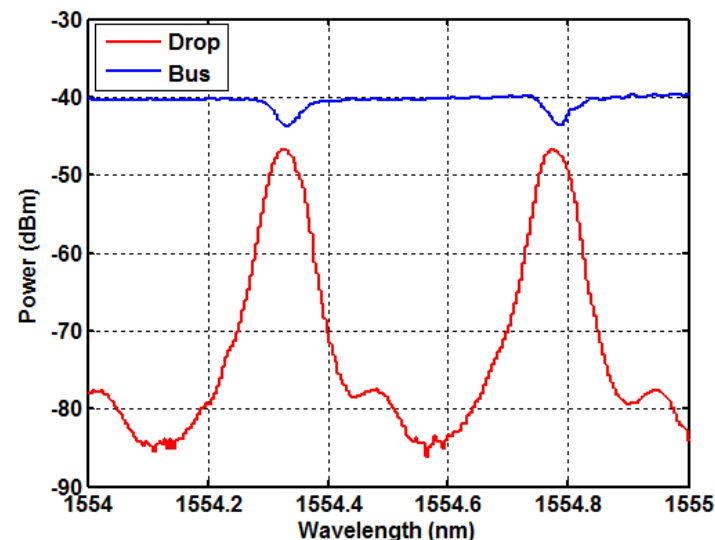


- SOAs enable monolithic integration
- Introduce an ideal loop gain to each filter
 - No noise in model, yet
- Ring waveguide loss
 - 4 dB/cm
- Loss-less filter achieved
 - 0.5 dB/pass gain element

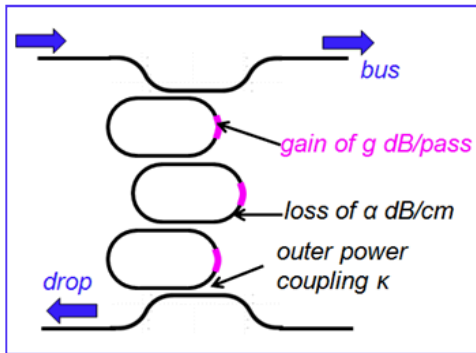
Active Rings : Experimental

See paper OThW2
Thur. @ 4 pm

- Dual-ring filters
 - > 30 dB extinction ratio
 - 2.5 GHz linewidth
 - $I_{\text{SOA1}} = I_{\text{SOA2}} = 1 \text{ mA}$
 - Extinction ratio of >30 dB
 - Filter loss of 1.7 dB
 - Loss defined as total power on resonance compared to total power off resonance
- OSA measurement
 - Broadband light source



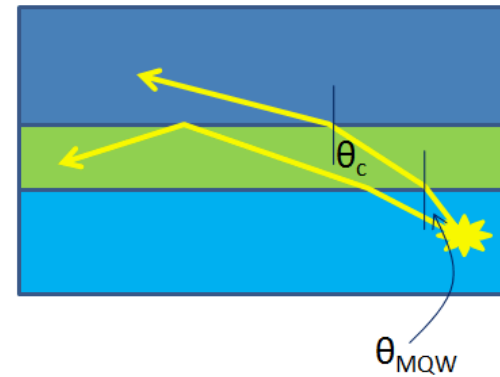
Active filter modeling



- Time domain travelling wave model of single and multi-ring filters
- Semiconductor Optical Amplifier (SOA) embedded in each ring
- Local gain and spontaneous emission modeled as functions of injection current and optical power
 - Time-dependent rate-equation approach
- Complete power spectra computed at each time step

Fraction of SOA spontaneous emission coupled into waveguide mode

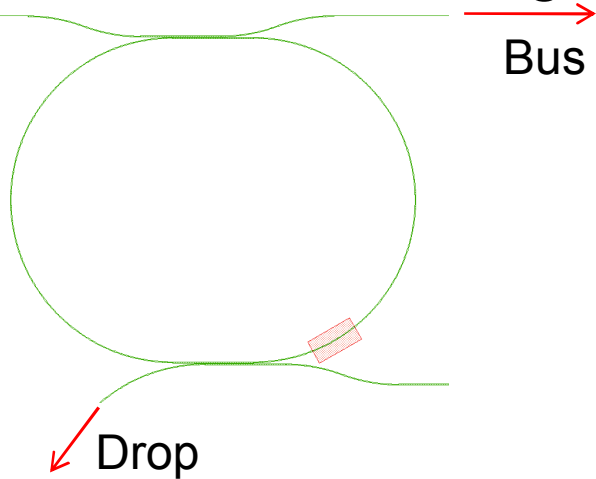
- Amplified spontaneous emission (ASE) noise from SOAs creates a noise floor on filter spectra
- ASE noise computation in two steps
 - Spontaneous emission recombination event
 - Coupling of spontaneous emission into guided mode of ring
- The spontaneous emission factor influences the noise floor due to ASE



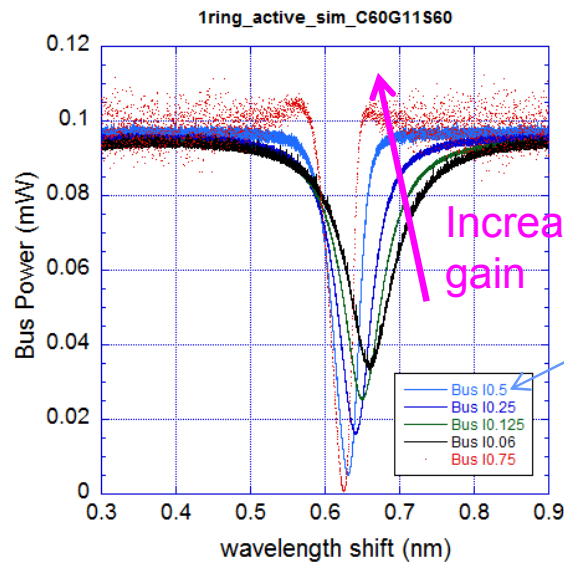
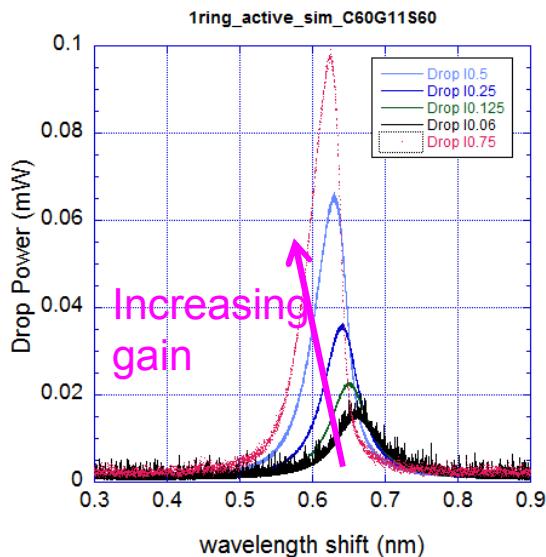
- Indexes
 - InP, $n = 3.168$
 - Q13, $n = 3.3877$
 - MQW, $n = 3.427$
- Included angle of captured light
 - 44.8 deg
- Area of spherical cap
 - $A_{cap} = 2\pi r h$
 - $H = r(1 - \cos\theta)$
- Area of sphere
 - $A_{total} = 4\pi r^2$
- Fractional area
 - $A_{cap}/A_{total} = (1 - \cos\theta)/2$
 - $\theta = 22.4$ deg
 - Fractional area = 0.0378
- Fraction of light capture by guided mode
 - Multiply fractional area by overlap integral with guided mode
 - $\Gamma(\text{fractional area}) = 0.06989 \times 0.0378 = 0.00264$
- $SponBetaNA = 0.00264$

Model of Active Ring

0.1 mW
1.54 \pm Δ μ m



Radius: 200 μ m
Couplers: 17% power cross-coupling
Passive guides: 3 cm^{-1}
SOA: 60 μ m long
7 QW centered, 25C
1 μ m wide BH
current flow *only* in the MQW
Spontaneous Coupling: 0.0037



$J = 830 \text{ A/cm}^2$
 $I = 0.5 \text{ mA}$

- Variation of SOA injection current
 - Insertion loss drops and bandwidth narrows as SOA current is increased

Model of Active Ring

0.1 mW
1.54 \pm Δ μ m

Bus

Drop

Radius: 200 μ m

Couplers: 17% power cross-coupling

Passive guides: 3 cm^{-1}

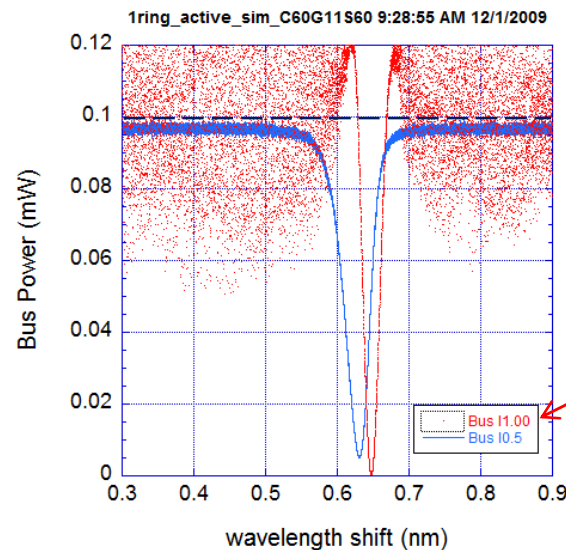
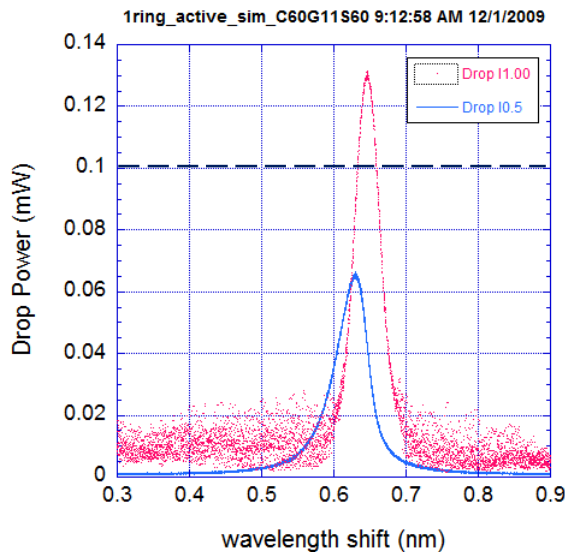
SOA: 60 μ m long

7 QW centered, 25C

1 μ m wide BH

current flow *only* in the MQW

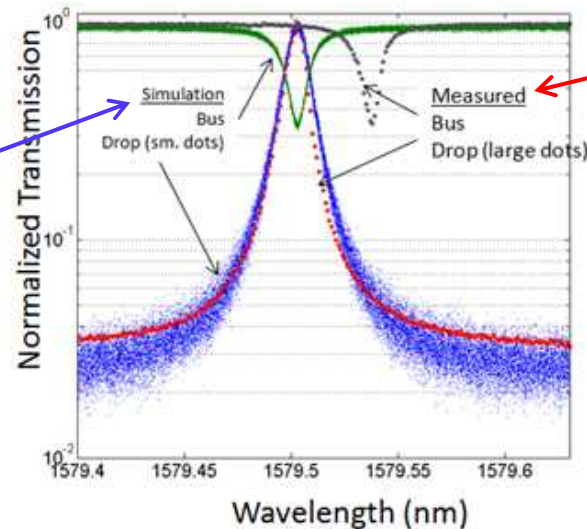
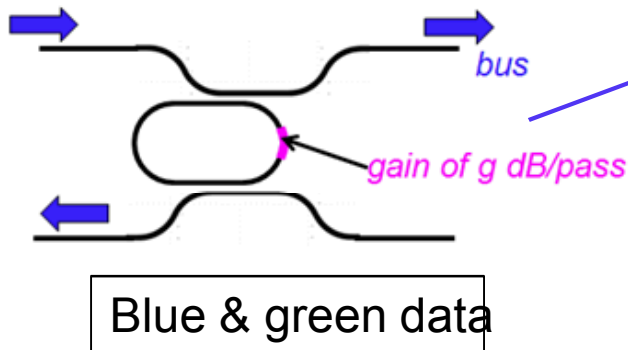
Spontaneous Coupling: 0.0037



$J = 1.67 \text{ KA/cm}^2$
 $I = 1.0 \text{ mA}$

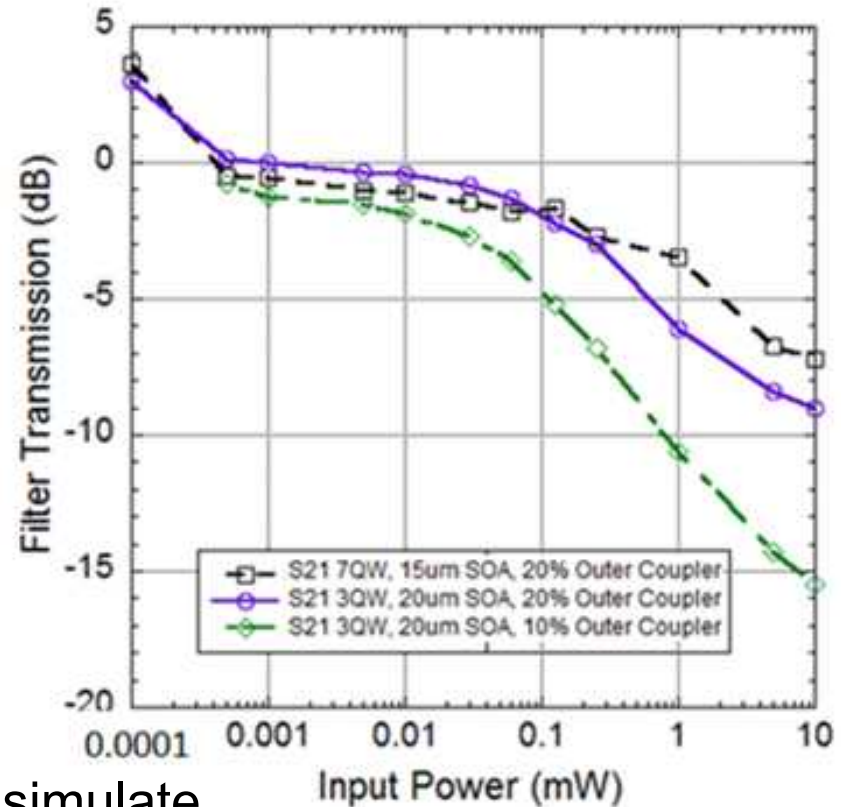
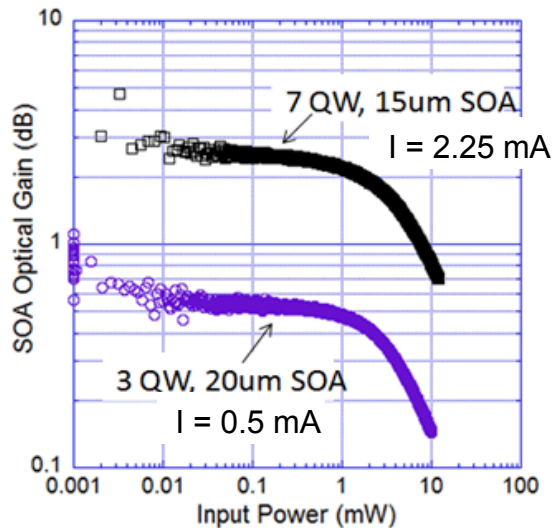
- Operation at very high gain (SOA injected current)
 - Negative insertion loss achievable, but very noisy

Single Ring Active Filter: Simulation Benchmark to Experiment



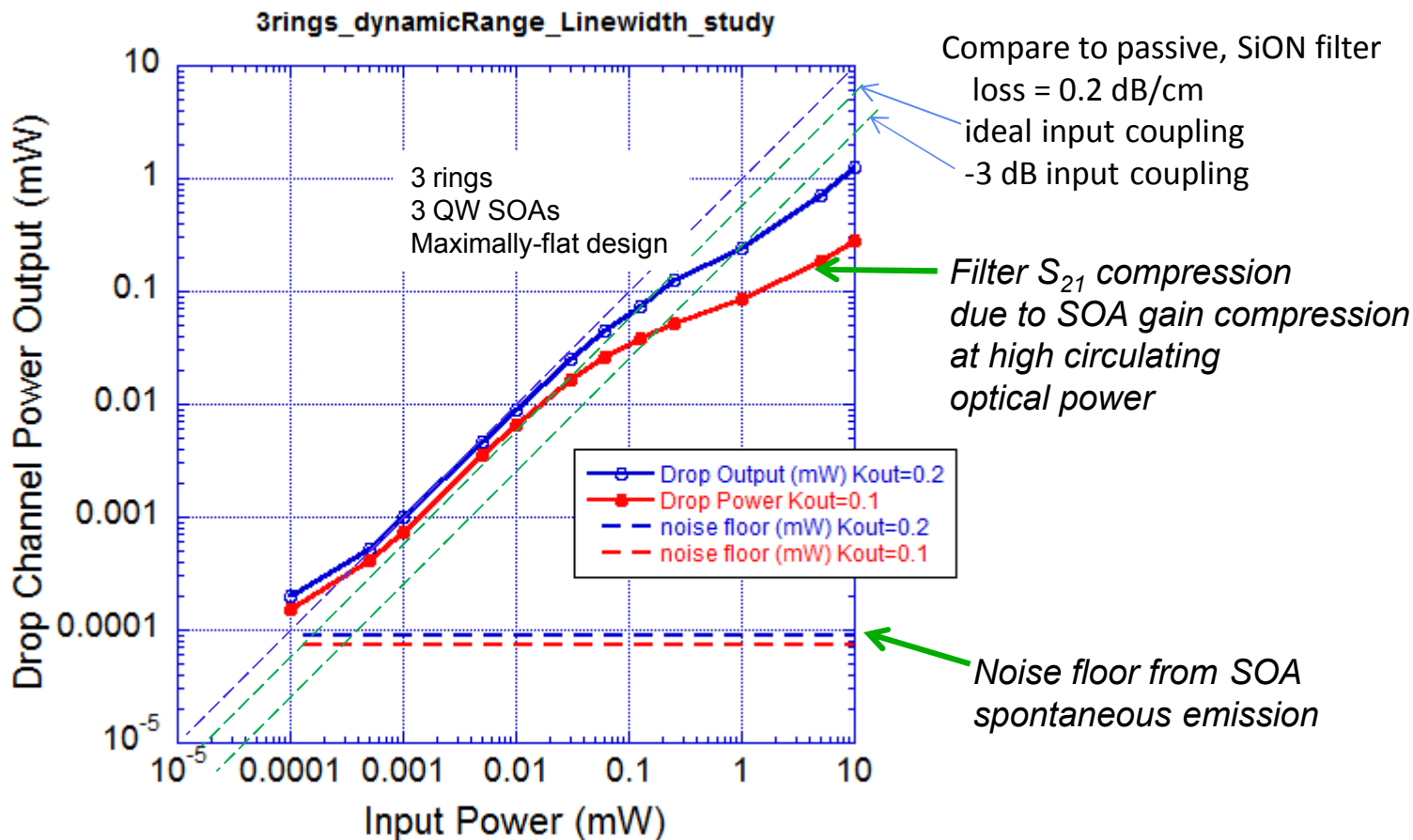
- Complete simulation of dynamic range and noise of active InGaAsP multi-ring filters
 - Include gain distortions and spontaneous emission noise
- Time dependent rate equation method
 - Gain and spontaneous emission modeled as function of injection current at all wavelengths simultaneously

3-ring active filter simulations



- For 3-ring maximally flat filters simulate
 - Linewidth, Insertion loss
 - Dynamic range and Noise floor
- SOA gain and power saturation depend on key factors
 - Number and configuration of QWs and Injected current
 - Simulate case of both 3 and 7 QW SOA

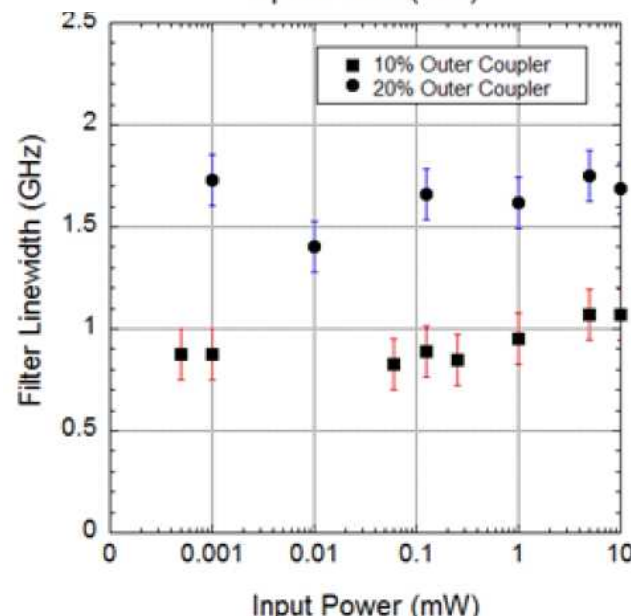
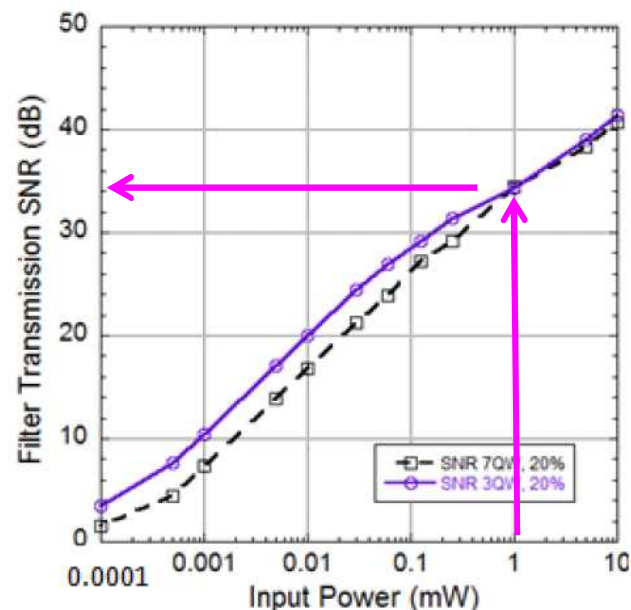
InP Filter Dynamic Range



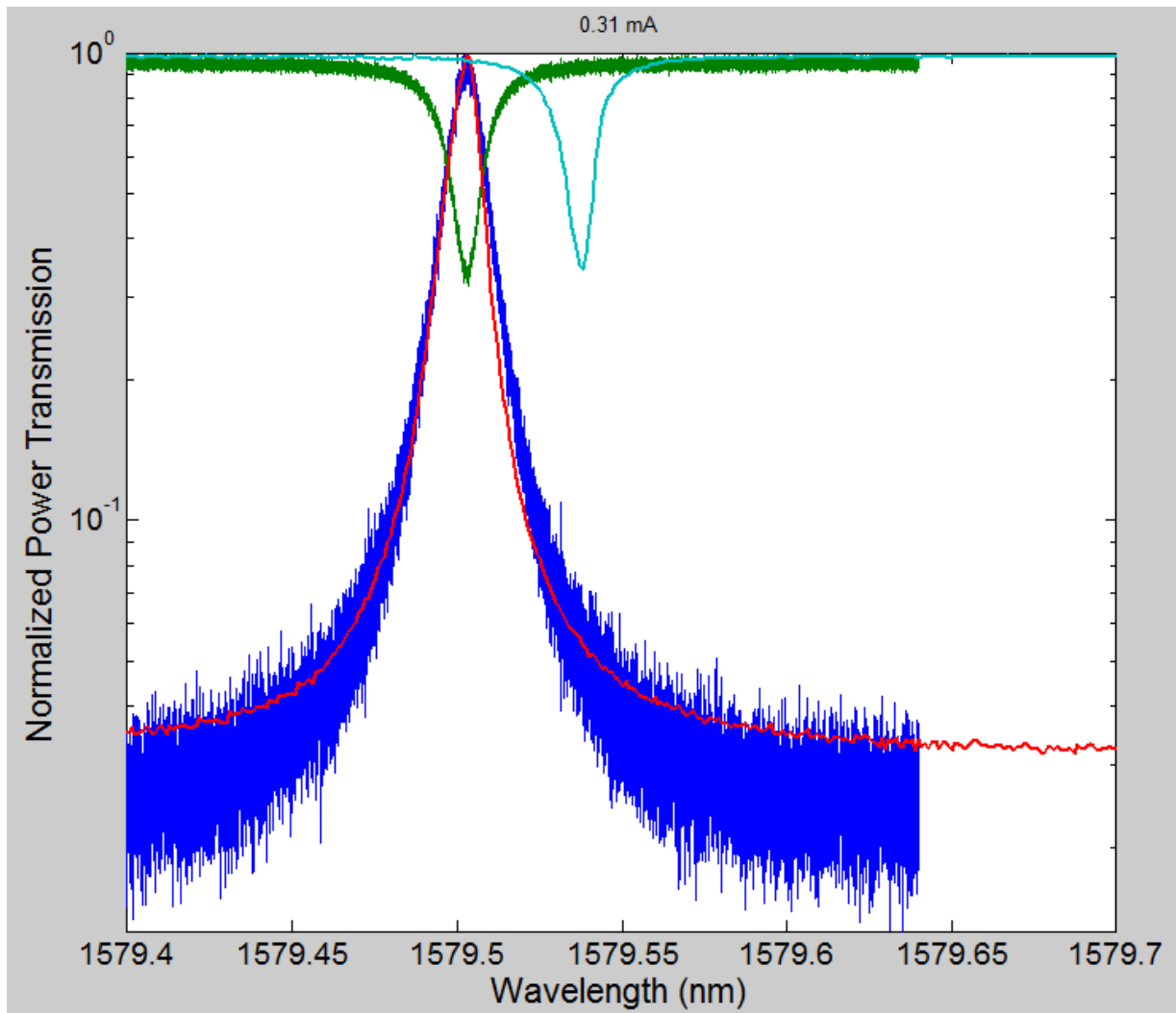
- Active InGaAsP filter shows improved filter transmission compared to passive SiON design over >30 dB dynamic range
- Spontaneous emission noise in SOAs limits SNR at lowest input optical powers
- SOA saturation causes compression of filter S_{21} at resonance at high end of input power

Summary

- Time domain model of active ring with SOAs developed
 - SOA model includes gain saturation and ASE
- 3-ring filter with 3 and 7 quantum well gain sections simulated
 - Optical linewidth
 - Noise floor
 - Linearity and dynamic range of S_{21} versus input power
- InP active filters show promise for frequency-domain signal processing in monolithic integrated photonic integrated circuits
 - 50 dB input dynamic range
 - Output compressed at high power
 - 0 dB loss in mid range accessible for 1 GHz filters
 - Filters with power gain are possible but quickly become limited by noise
 - Possible methods to improve dynamic range
 - Reduce optical confinement factor
 - Balance against lower gain or more complex offset active lasers in remainder of PIC
 - Wider SOAs
 - More pump current



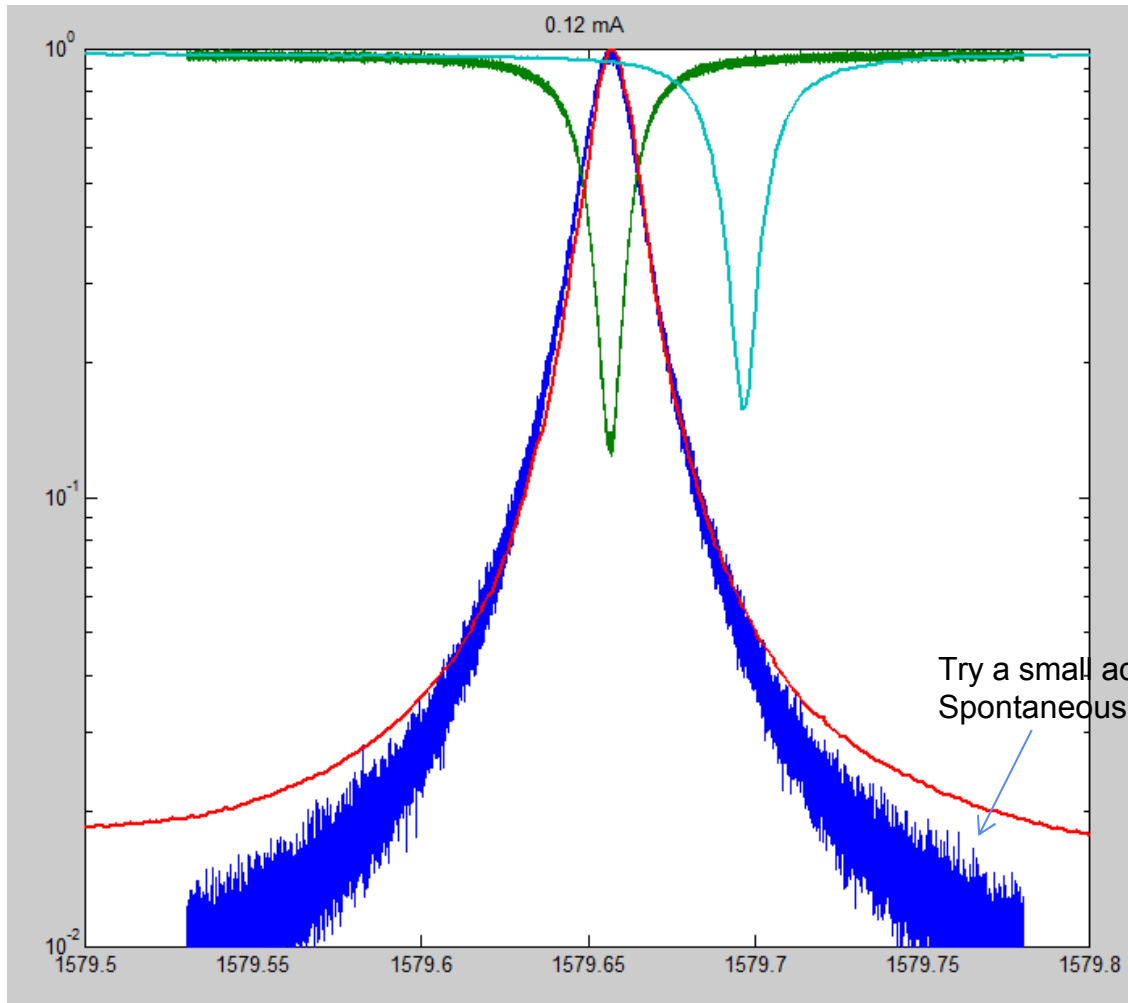
Best Fit to C20G10S100, EW1858



- 8 QW offset
- 100 μm SOA
- $K^2 = 0.03$
- Loss = 1.4 cm^{-1}
- $P_{\text{in}} = 0.005$ mW
- I_{SOA} model
 - 0.31 mA
- I_{SOA} exp
 - 1 mA

Simulation data is in SOA100_K03_alpha14_8mqw_offset.xls and .mat

Detail Fit to C40G10S20, EW1858



- 8 QW offset
- 20 μm SOA
- $K^2 = 0.06$
- Loss = 1.4 cm^{-1}
- $P_{\text{in}} = 0.005$ mW
- I_{SOA} model
 - 0.12 mA
- I_{SOA} exp
 - 0.2 mA
- P_{in} exp
 - 0.2 mW

Simulation data is in SOA20_K06_alpha14_8mqw_offset.xls and .mat